

# ECEN720: High-Speed Links Circuits and Systems

## Spring 2025

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### Lecture 16: Optical Transceivers



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# Announcements

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- Project Final Report due Apr 29
- Exam 2 May 2
  - 1PM-3PM for in-person sections
  - Focuses on material from Lectures 7-15
  - Previous years' Exam 2s are posted on the website for reference

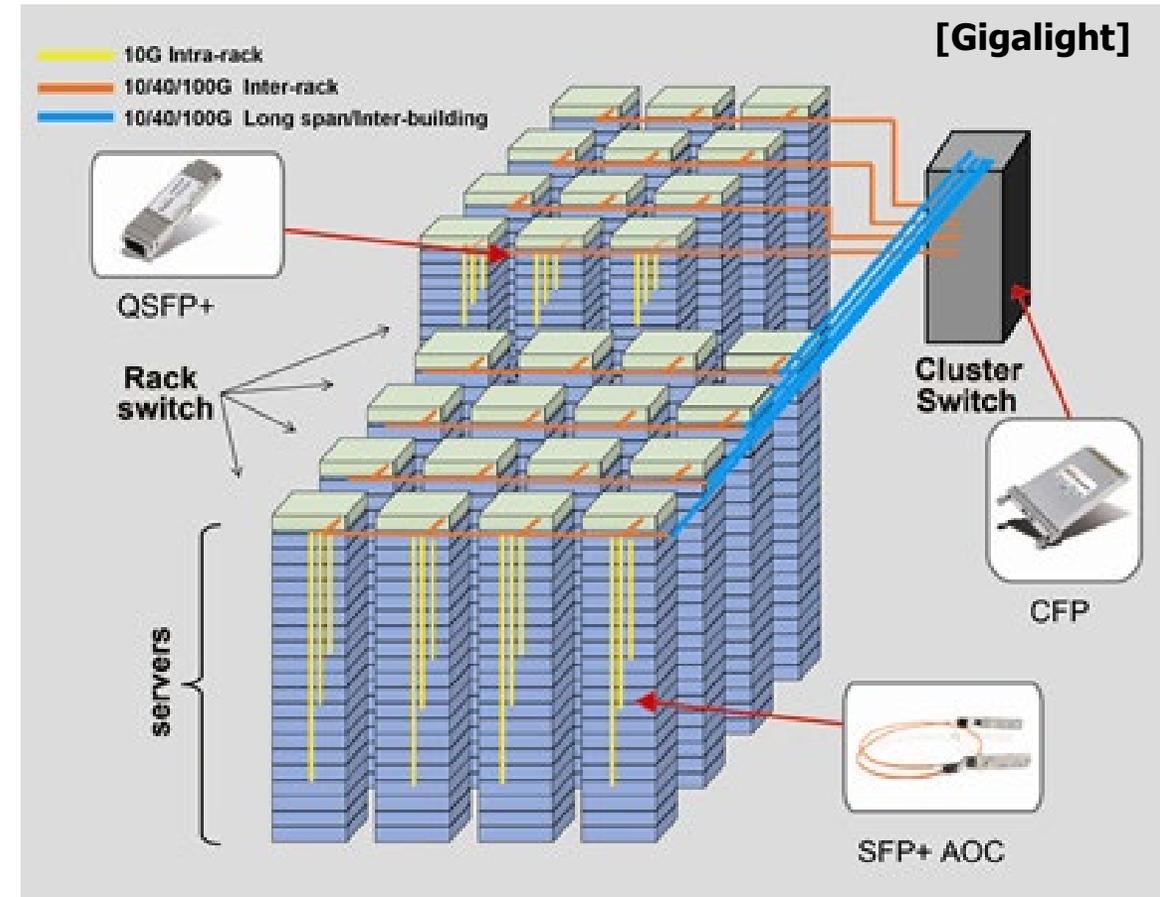
# Outline

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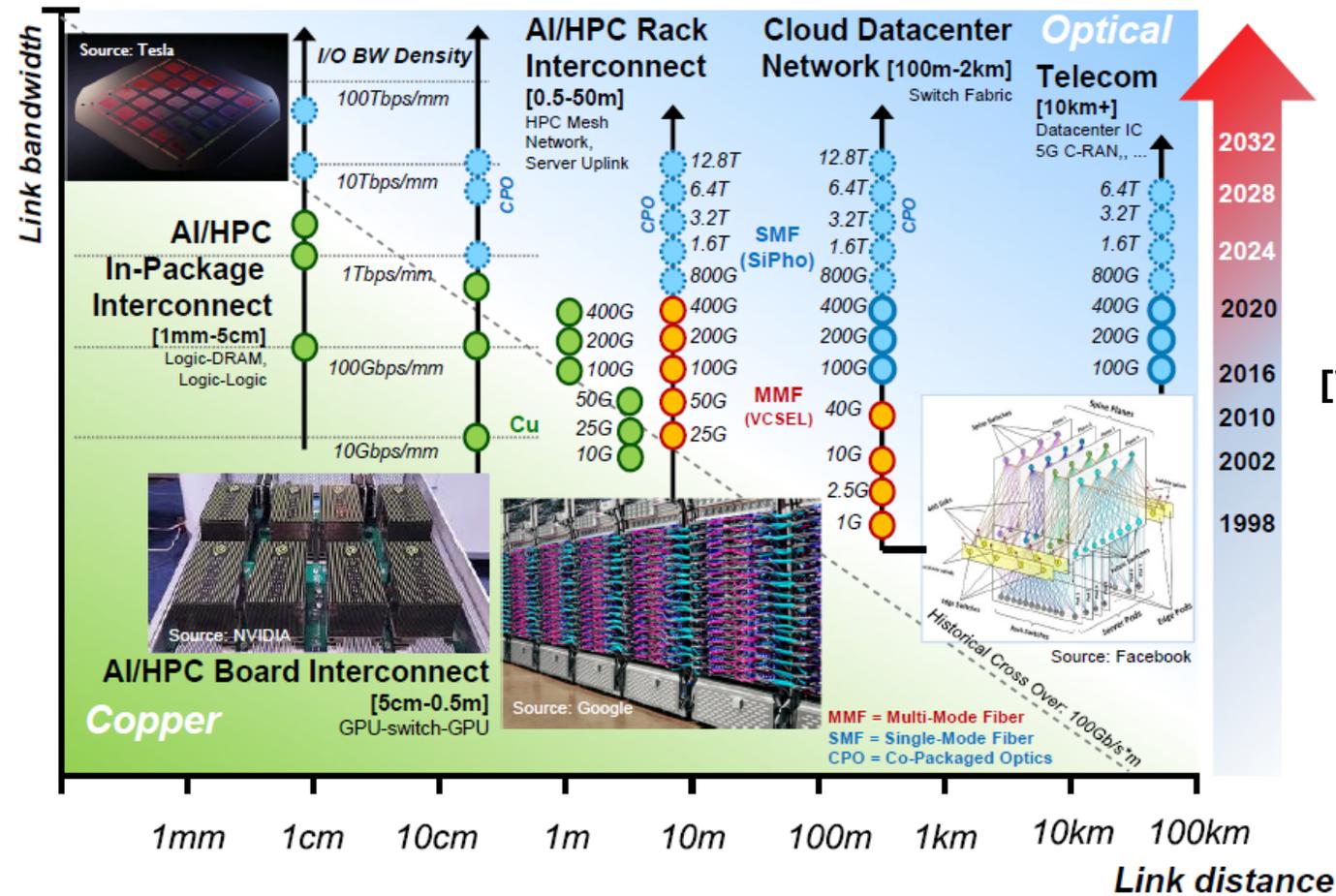
- Optical Interconnect Motivation
- Optical Channel Properties
- IMDD and Coherent Transceivers
- Transmitter Properties and Devices
- Receiver Architecture and Devices
- Conclusion

# Data Center Links

- Different interconnect technologies are used to span various distances
- Electrical I/O
  - Chip-to-module
  - Intra-rack (DAC cables)
- Optical I/O
  - Intra-rack (AO cables)
  - TOR switch to edge switch



# Data Center Link Length



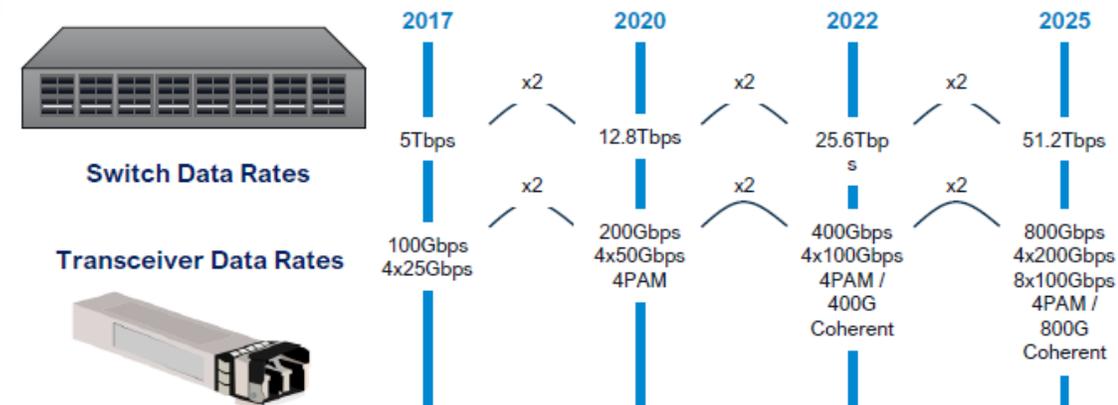
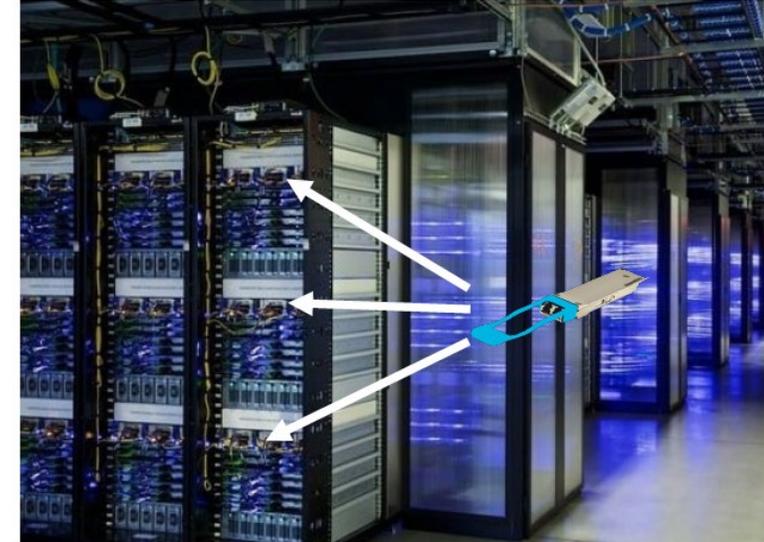
[Van Campenhout ISSCC 2022]

- Maximum reach scales inversely with data rate

# AI Datacenter Connectivity Demands

- Scaling up with more xPUs in compute clusters
- Scaling out to larger clusters
- Higher per-lane data rates
- Flatter network topologies with higher radix switches to reduce latency
- Pushing optical connectivity to within the rack

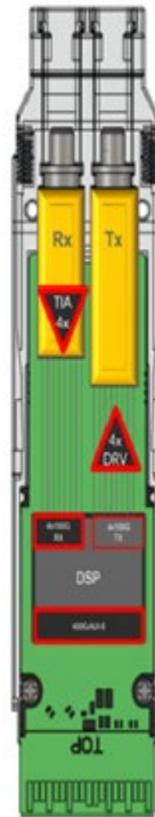
[Wang ISSCC 2024]



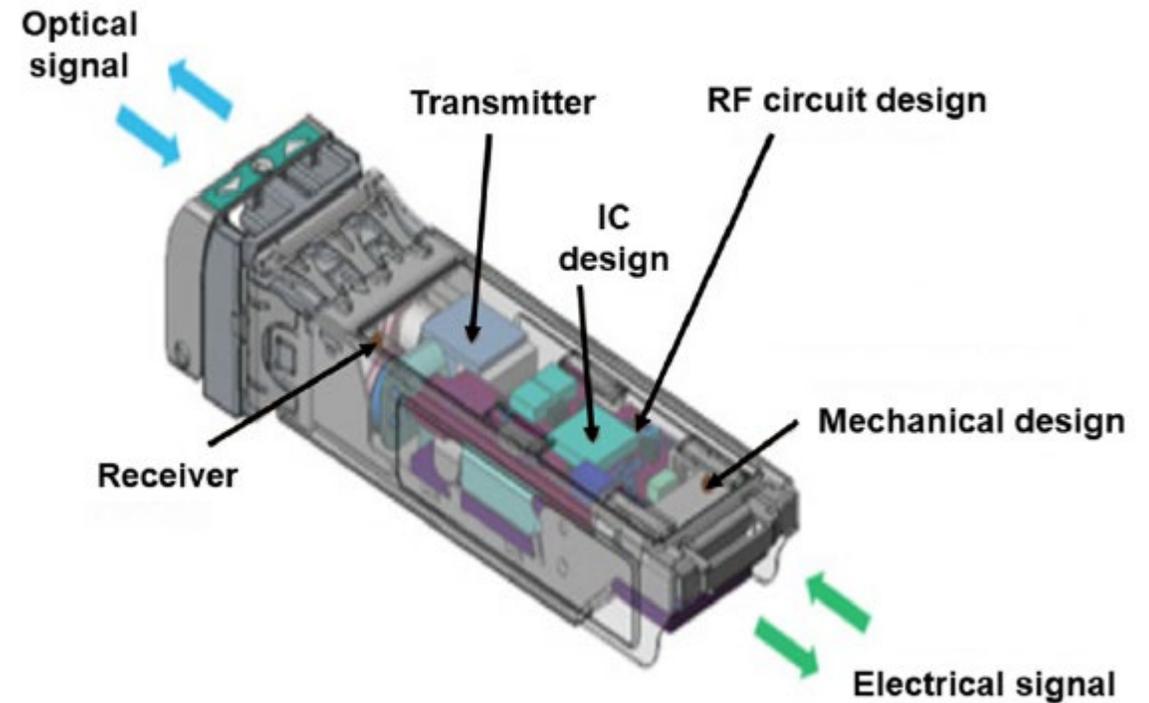
[Chan Carusone ISSCC 2024] 6

# Optical Modules

- Retimed pluggable modules
  - TX/RX DSP in advanced node CMOS
  - Separate driver and TIA chips, which can be SiGe, InP, CMOS
- Linear optics
  - Remove DSP to save power
  - Need to be very linear and have high bandwidth

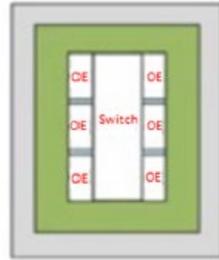


[Lau JEP 2025]

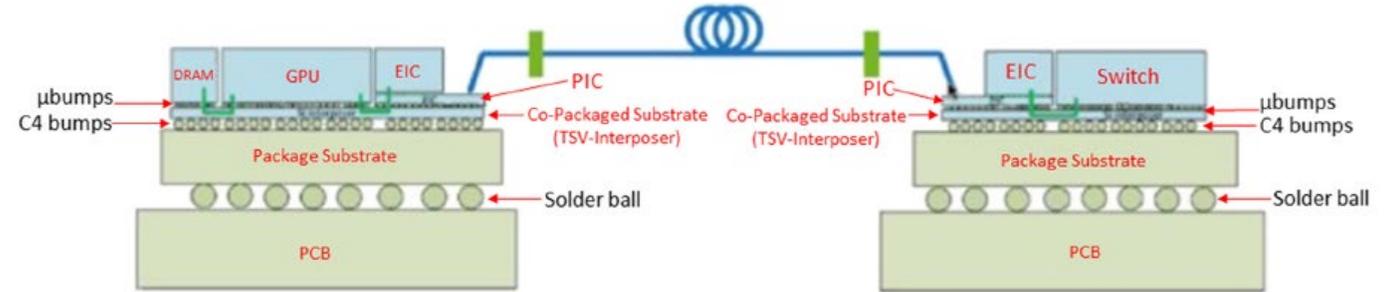


# NVIDIA CPO Example

[NVIDIA GTC 2025]



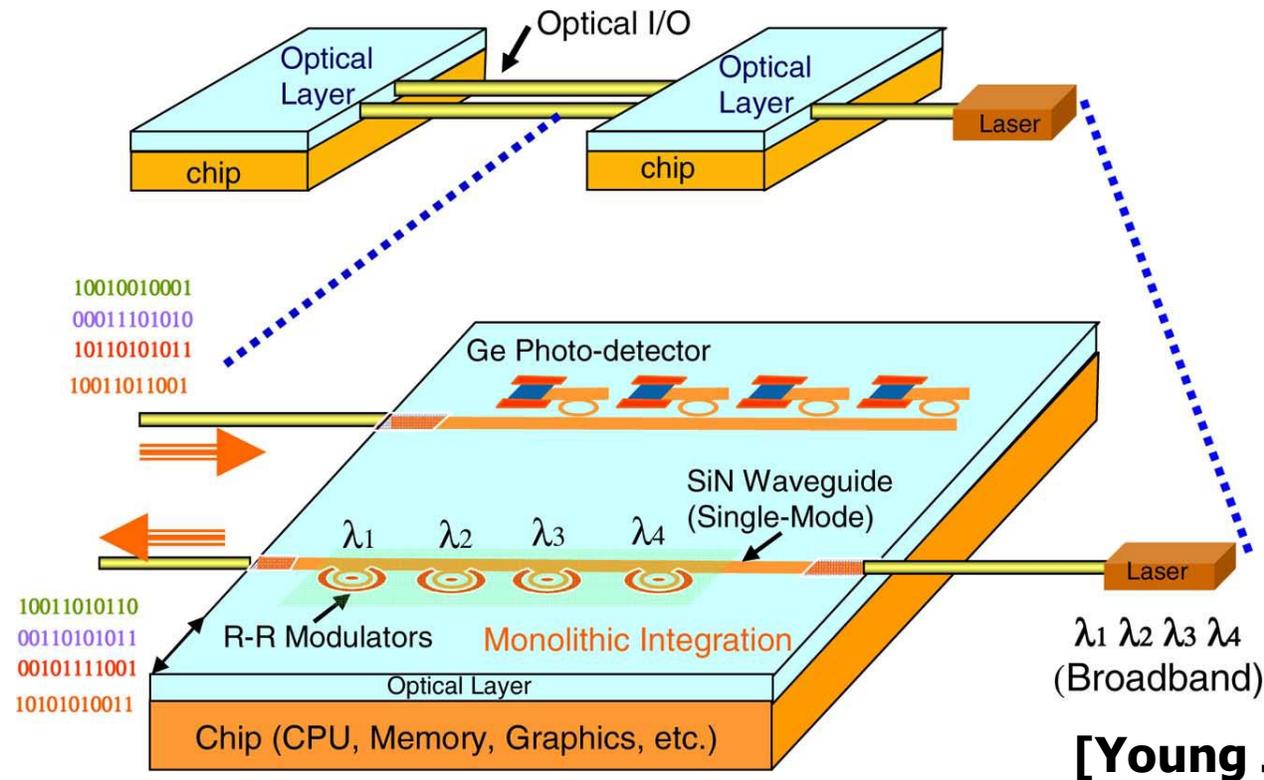
[Lau JEP 2025]



- 4x28.8Tb/s Switch

- Based on microring resonator modulators driven by 200Gb/s PAM4 SERDES
- 3D hybrid bonding for EIC-PIC interface
- External laser source
- 6 optical assemblies X 3 photonic engines
- 288 data link fibers per 28.8Tb/s plus 36 laser fibers

# Wavelength-Division Multiplexing (WDM)



- WDM allows for multiple high-bandwidth (10 - 200Gb/s) signals to be packed onto one optical channel

# Outline

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- Optical Interconnect Motivation
- **Optical Channel Properties**
- IMDD and Coherent Transceivers
- Transmitter Properties and Devices
- Receiver Architecture and Devices
- Conclusion

# Optical Channels

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- Short distance optical I/O channels are typically waveguide (fiber)-based
- Optical channel advantages
  - Much lower loss
  - Lower cross-talk
  - Smaller waveguides relative to electrical traces
  - Potential for multiple data channels on single fiber via WDM

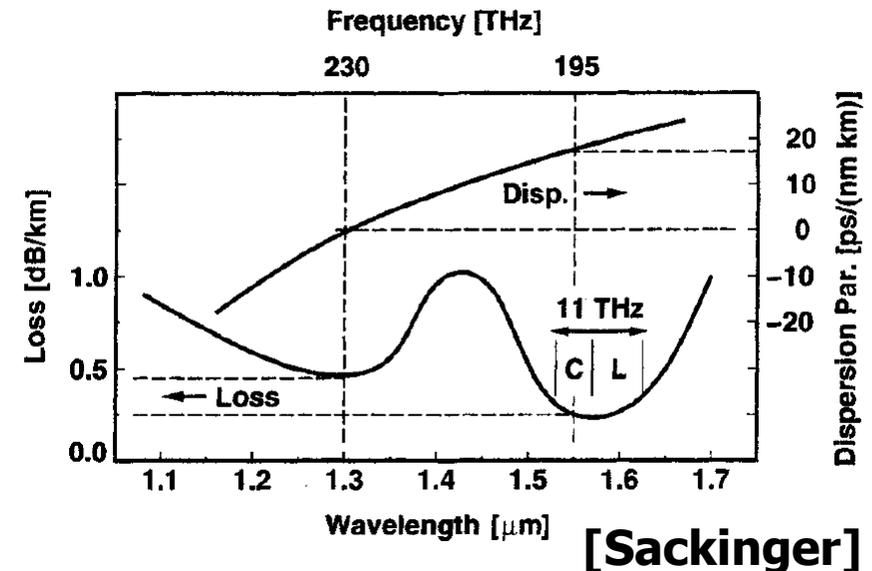
# Waveguide (Fiber)-Based Optical Links

- Optical fiber loss is specified in dB/km
  - Single-Mode Fiber loss  $\sim 0.25$  dB/km at 1550 nm
  - RF coaxial cable loss  $\sim 100$  dB/km at 10 GHz
- Frequency dependent loss is very small
  - $< 0.5$  dB/km over a bandwidth  $> 10$  THz
- Bandwidth may be limited by dispersion (pulse-spreading)
  - Important to limit laser linewidth for long distances ( $> 1$  km)

## Optical Fiber Cross-Section



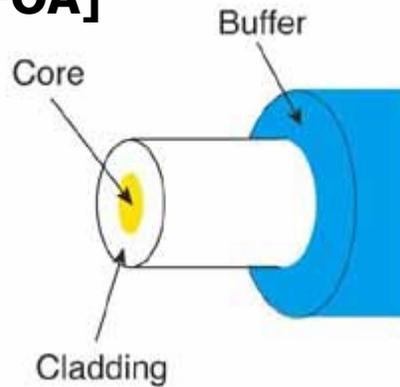
## Single-Mode Fiber Loss & Dispersion



# Optical Fiber Cross-Section

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[FOA]



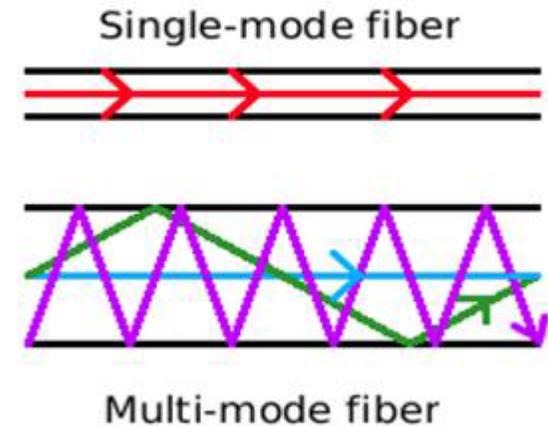
- Optical fibers confine light between a higher index core and a lower index cladding via total internal reflection

# Optical Fiber Modes

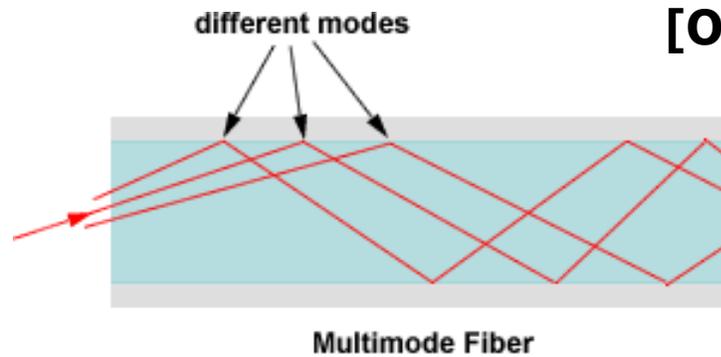
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- For light to propagate down the fiber, the interference pattern or **mode** generated from reflecting off the fiber's boundaries must satisfy resonance conditions
- Fibers are classified based on their ability to support multiple or single modes

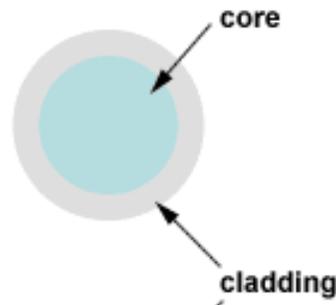
[Fibertronics]



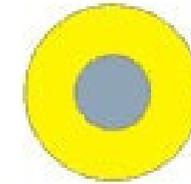
# Multi-Mode Fibers



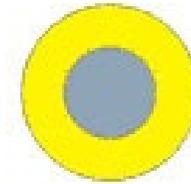
[Optical Fiber Tutorial]



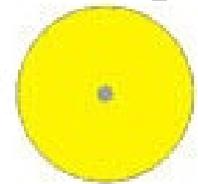
[FOA]



Multimode  
50/125  $\mu\text{m}$



Multimode  
62.5/125  $\mu\text{m}$

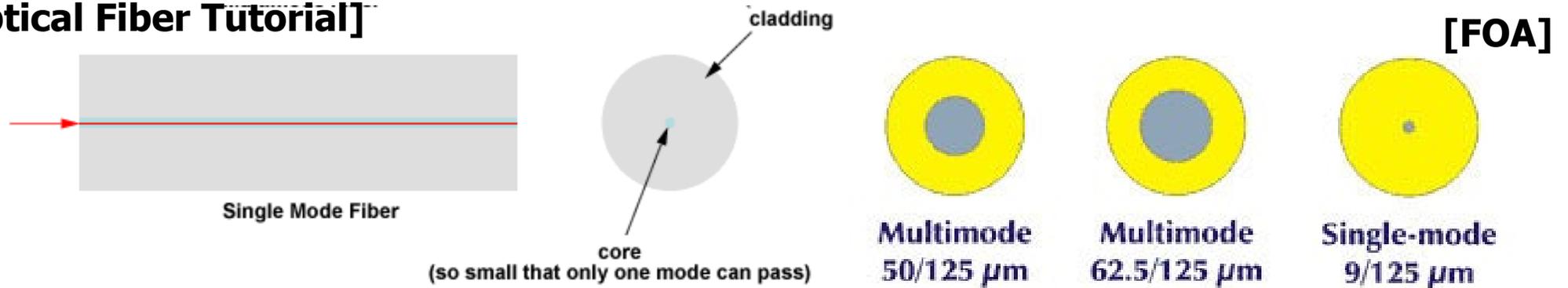


Single-mode  
9/125  $\mu\text{m}$

- Multi-mode fibers have large core diameters
  - Typically 50 or 62.5 $\mu\text{m}$
  - Relatively easy to couple light into
- The large diameter allows for multiple propagating modes
- Major performance limitation is modal dispersion caused by the different modes propagating at different velocities
- Typically specified with a bandwidth-distance product
  - Legacy MMF 200MHz-km
  - Optimized MMF >4GHz-km

# Single-Mode Fibers

[Optical Fiber Tutorial]

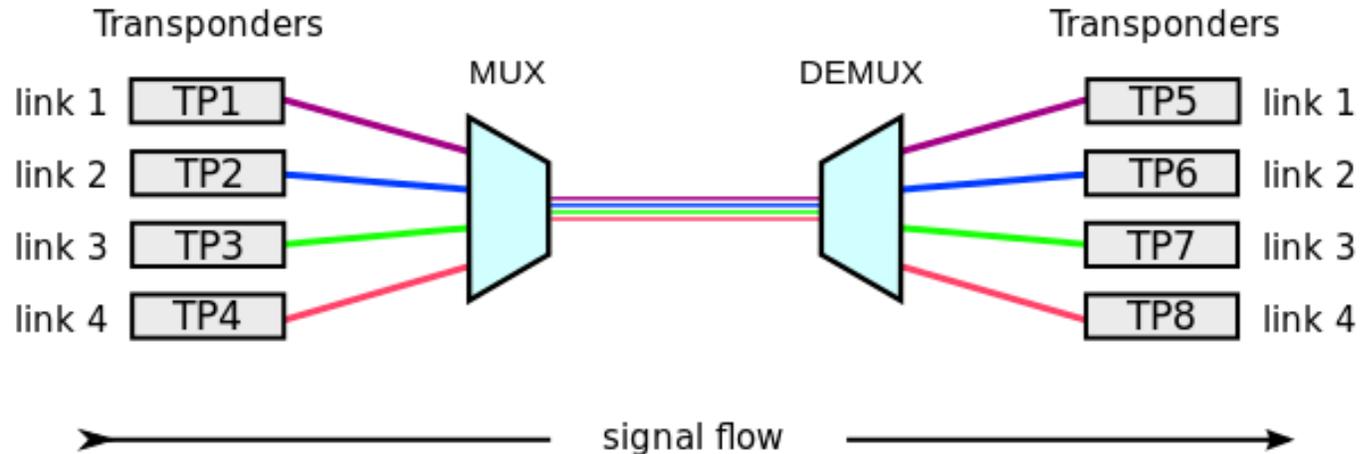


- Multi-mode fibers have much smaller core diameters
  - Typically 8-10μm
  - Requires careful alignment (cost)
- The small diameter allows for only one propagating mode (with two orthogonal polarizations)
- Allows for much longer transmission distances (>100km)
- At long distance, major performance limitation is fiber loss
- Chromatic- and polarization-mode dispersion can also limit performance, but generally negligible <10km

# Wavelength-Division Multiplexing (WDM)

## wavelength-division multiplexing (WDM)

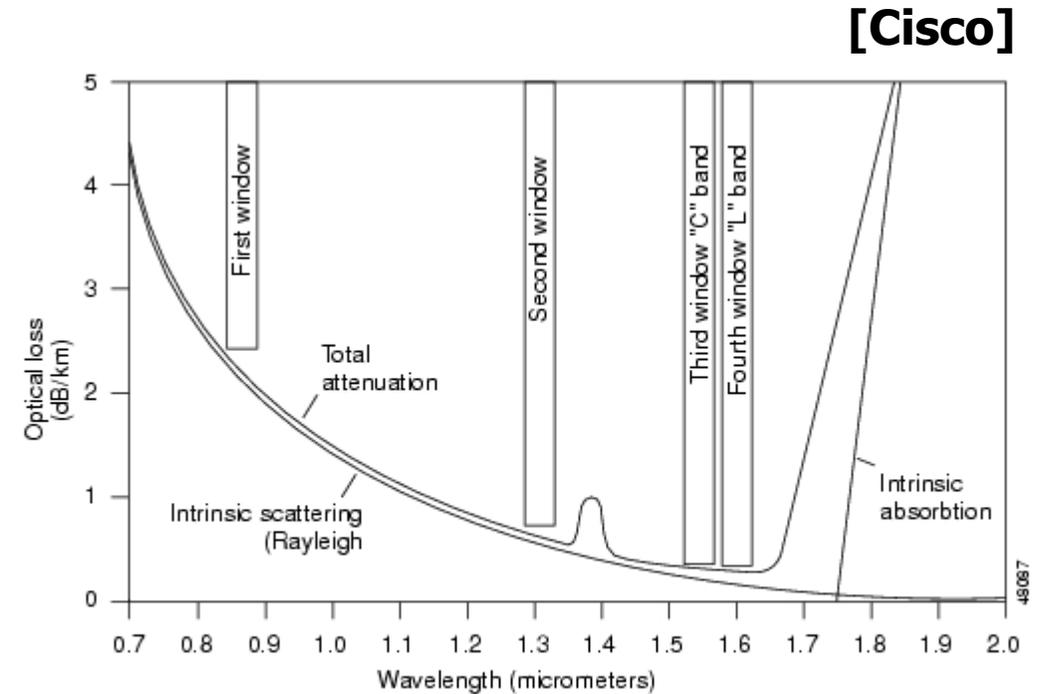
[Xens]



- While single-mode fibers only support one mode, one way to increase the bandwidth density is to use multiple wavelengths to transmit independent information
- This is called wavelength-division multiplexing (WDM)
- Allows efficient use of the several THz bandwidth of the optical fiber with many wavelengths independently modulated at 10s of Gb/s

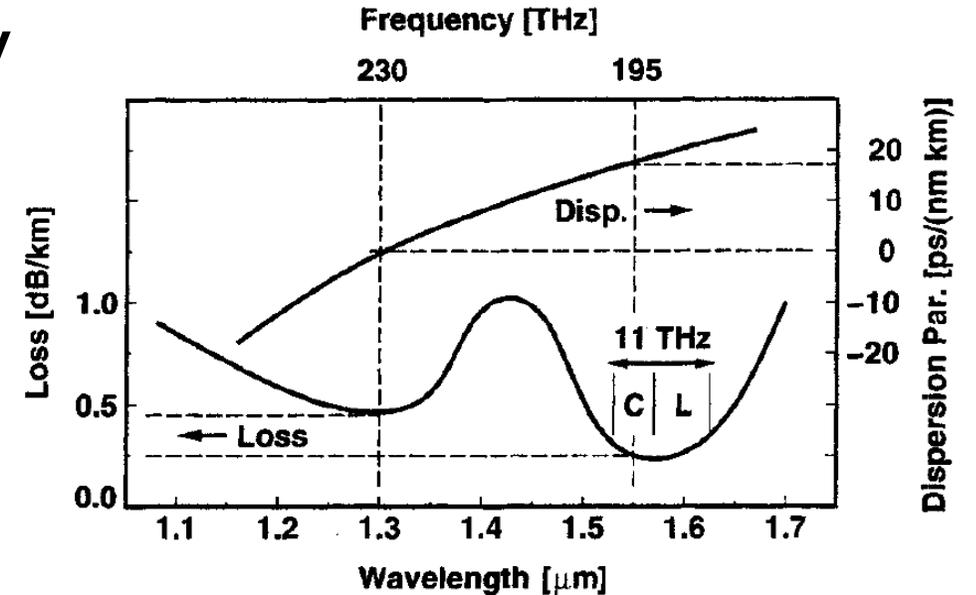
# Silica Glass Fiber Standard Transmission Windows

- Standard silica glass fiber has a loss minimum near 1550nm
  - This region occupies a bandwidth of 95nm or 11THz!
  - Divided into 2 bands or transmission windows
    - Conventional or C-band (1530 – 1565nm)
    - Long-wavelength or L-band (1565 – 1625nm)
- Another window popular for long distance is near 1310nm, where the fiber chromatic dispersion is near zero
  - Original or O-band (1260 – 1360nm)
- A window near 850nm (800 – 900nm) is also commonly used for short distance communication due to low-cost optical sources and detectors



# Fiber Bandwidth and Dispersion

- While optical fiber has very wide bandwidth over which there is very low loss, there are still limits to high-speed communication
- Optical fiber can disperse a broadband signal, as different spectral components travel at different speeds
- This is **Chromatic Dispersion**



[Sackinger]

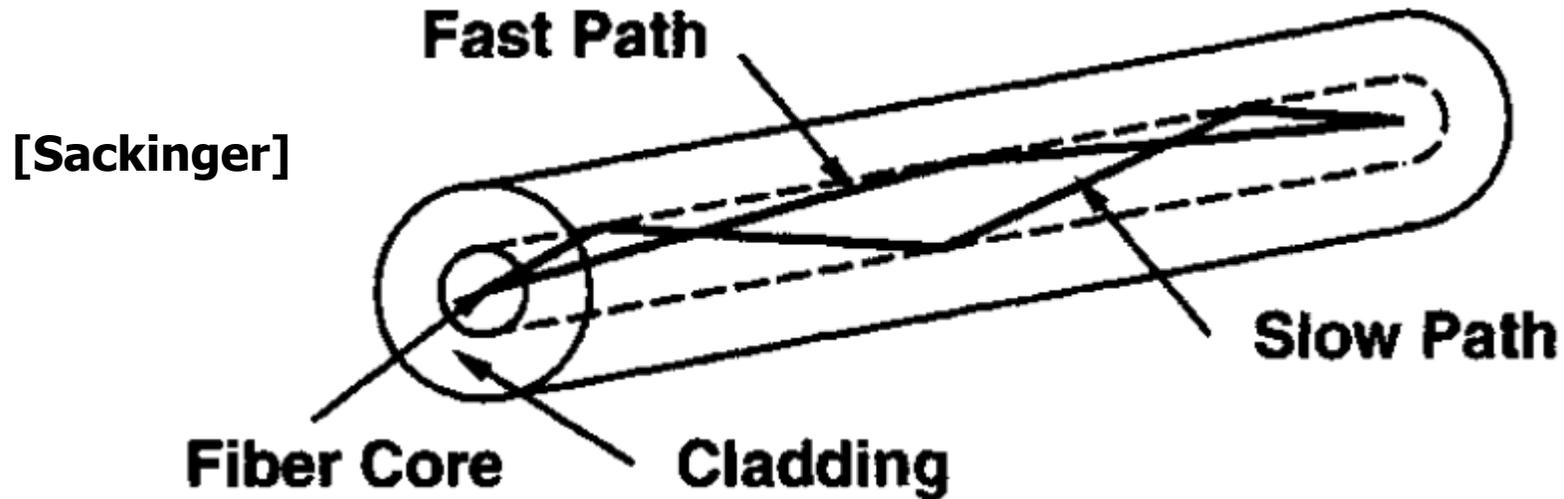
# Dispersion

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- Dispersion is the temporal spreading of high-speed pulses (bits)
  - Can cause intersymbol interference (ISI) and degrade BER
- Modal Dispersion
  - In a MMF, different modes of light travel at different speeds
- Chromatic Dispersion
  - In a SMF, different frequency content of a modulated optical carrier travels at different speeds
- Polarization-Mode Dispersion
  - In a SMF, different polarizations travel at different speeds

# Modal Dispersion

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- The multiple propagating modes in a MMF have different propagation delays
- This results in pulse spreading at the receiver end or **modal dispersion**

# Modal Dispersion Example

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- The pulse spreading is the time difference between the longest and shortest paths,  $\Delta T$

For a graded - index multimode fiber (GRIN - MMF)

$$\Delta T = \frac{(n_{cor} - n_{clad})^2}{8cn_{cor}} L$$

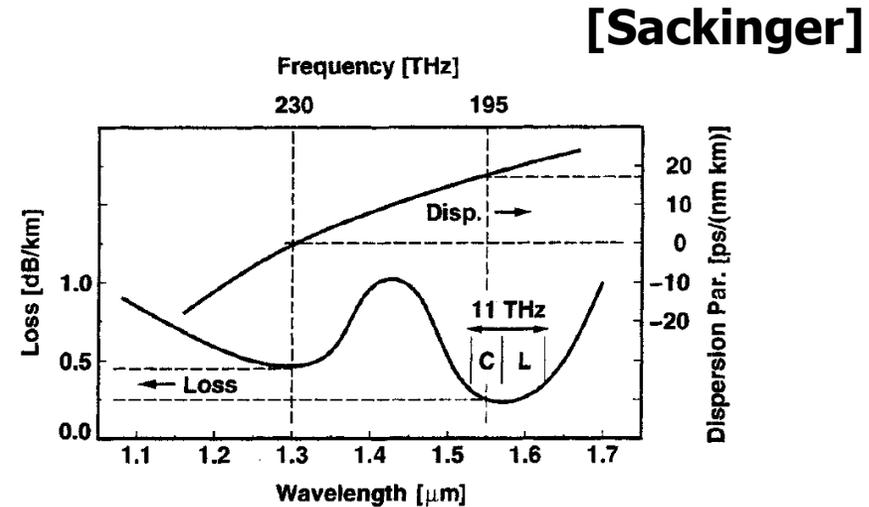
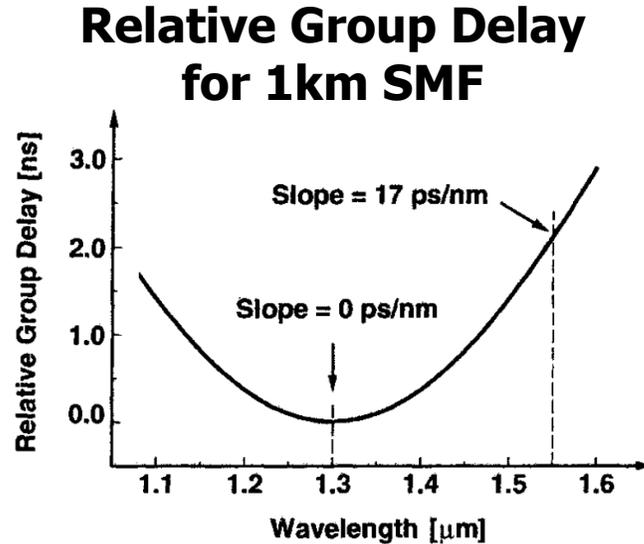
where  $L$  is the fiber length,  $c$  is the speed of light, and  $n_{cor}$  and  $n_{clad}$  are the core and cladding refractive indexes, respectively.

With  $n_{cor} = 1.48$ ,  $n_{cor} - n_{clad} = 0.02$ ,  $L = 1\text{km}$

$$\Delta T = \frac{(0.02)^2}{8 \left( 3 \times 10^8 \frac{m}{s} \right) 1.48} (1\text{km}) = 113 \text{ps}$$

- For this example, if we want this to be  $\sim 10\%$  of the bit period, then this limits the maximum data rate to less than 1Gb/s at 1km
- Optimized multi-mode fibers have  $>4\text{GHz-km}$

# Chromatic Dispersion



- Different wavelengths travel at different speeds down a fiber, resulting in group-velocity or **chromatic dispersion**
- Specified by the change in group delay ( $\tau$ ) per nm wavelength and km distance

$$\text{Dispersion Parameter: } D = \frac{1}{L} \cdot \frac{\partial \tau}{\partial \lambda}$$

- Standard SMF has  $D=17\text{ps}/(\text{nm} \cdot \text{km})$  at 1550nm

# Chromatic Dispersion Pulse Spreading

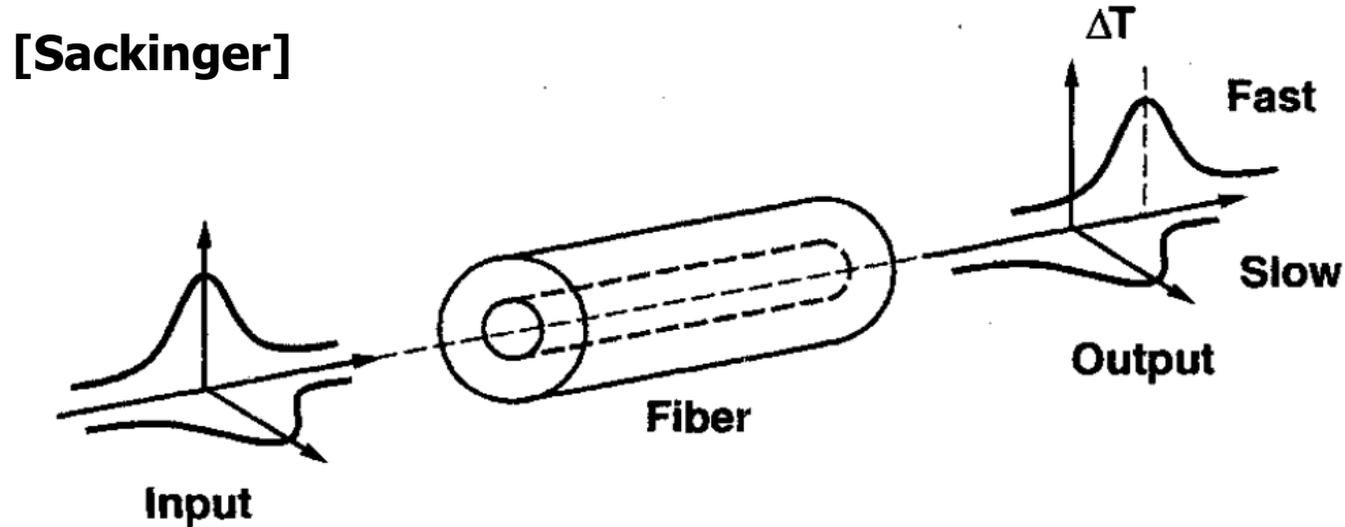
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- Chromatic dispersion is a function of the transmitter spectral linewidth ( $\Delta L$ ) (the nm in the denominator)
- The transmitter linewidth is a function of
  - Source laser phase noise
  - Modulation scheme
  - Modulation technique (direct vs external)
- Chromatic dispersion pulse spreading

$$\Delta T = |D| \cdot \Delta \lambda \cdot L$$

- For a 1nm spectral linewidth source, the signal will spread by 17ps over 1km of standard SMF with  $D=17\text{ps}/(\text{nm}\cdot\text{km})$  at 1550nm

# Polarization-Mode Dispersion



- While a SMF can only support one pathway or transverse mode, the transmitter typically has both horizontal and vertical polarization modes which both propagate down the fiber
- If a fiber has a slightly elliptical core or experiences asymmetrical mechanical stress, then the two polarization modes travel at different speeds and **polarization-mode dispersion** (PMD) results

# Polarization-Mode Dispersion Pulse Spreading

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- The fiber's effect on the polarization changes randomly along its length, making PMD have statistical uncertainty
- The pulse spreading, averaged over multiple fibers, is

$$\overline{\Delta T} = D_{PMD} \sqrt{L}$$

where  $D_{PMD}$  is the polarization - mode dispersion parameter

- PMD is also a time-varying parameter, which can complicate compensation

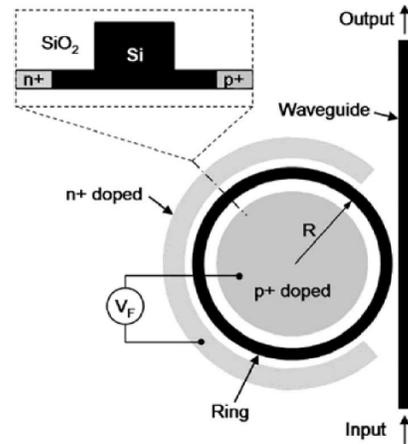
# Polarization-Mode Dispersion Mitigation

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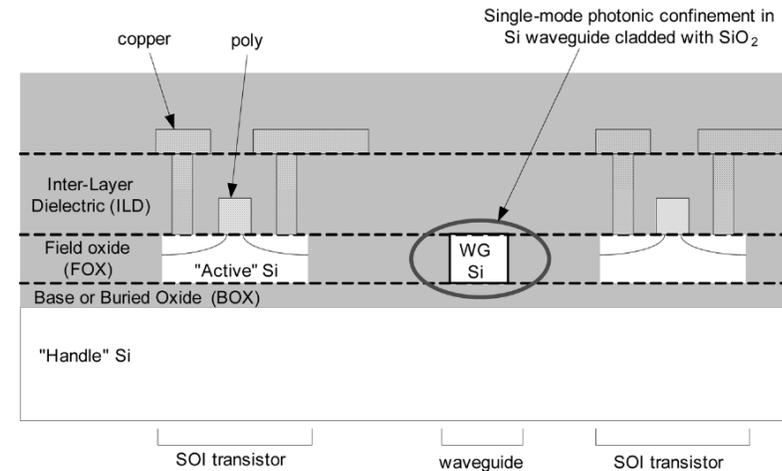
- Luckily, PMD is not too bad
  - Legacy fiber  $D_{\text{PMD}}=2\text{ps}/\sqrt{\text{km}}$
  - New fiber  $D_{\text{PMD}}=0.1\text{ps}/\sqrt{\text{km}}$
- For data center scale interconnects (<10km), PMD can generally be neglected
- Long-haul mitigation techniques
  - Short polarization maintaining fiber with adaptively-controlled polarization controlled
  - Adaptive electronic equalizer

# Silicon Photonic Waveguides

## Ridge waveguide used in a ring resonator modulator



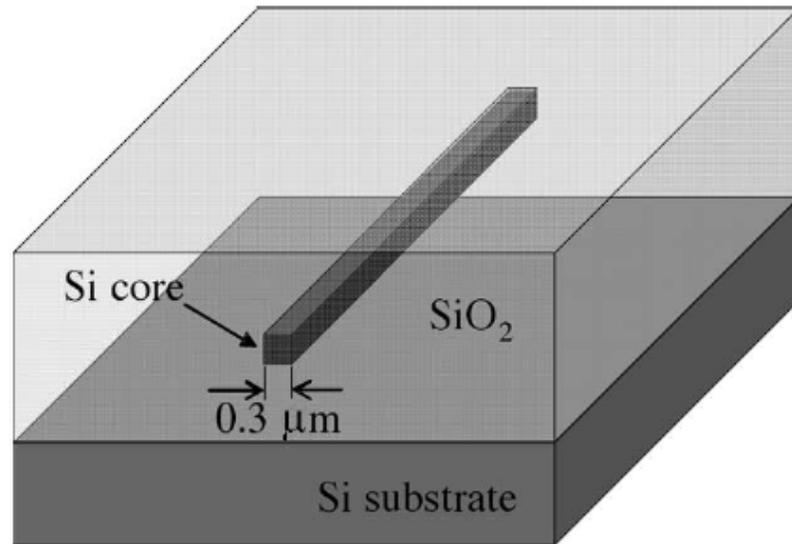
## Wire/rectangular waveguide



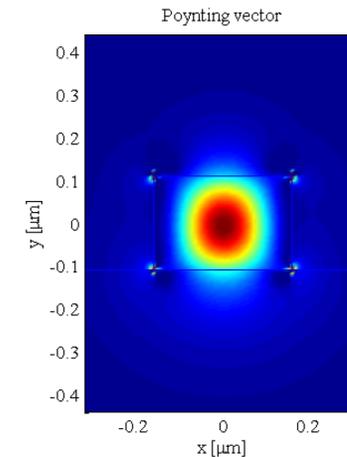
- Waveguides can be made in CMOS processes with a silicon core surrounded by an SiO<sub>2</sub> (or similar) cladding
- Common structures are the "ridge" and "wire/rectangular" waveguides

# Silicon Photonic Waveguides

## Wire/rectangular waveguide



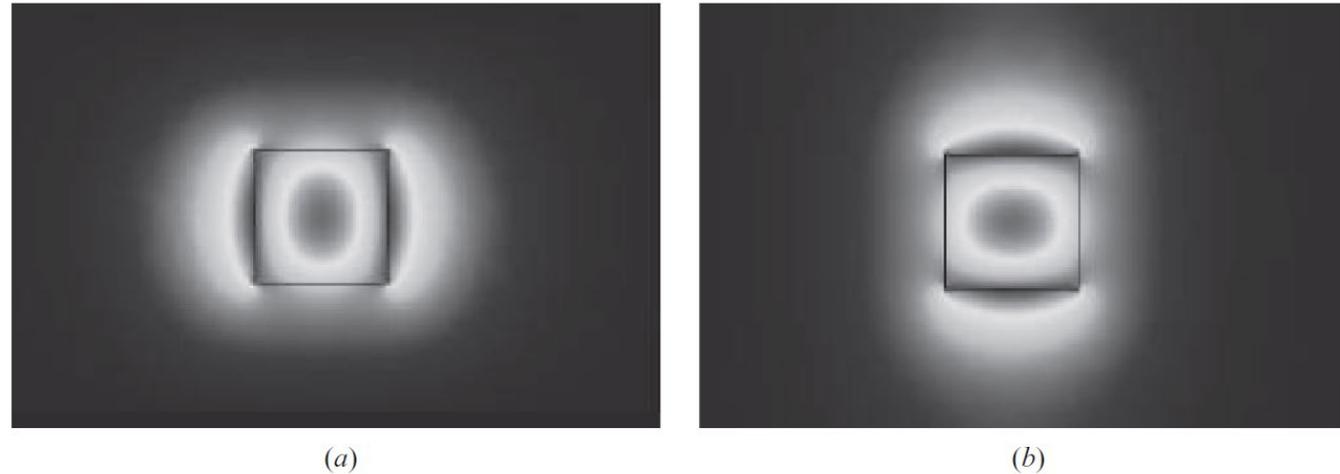
**Width = 320nm**  
**Height = 220nm**



- The high index contrast between Si ( $\sim 3.5$ ) and SiO<sub>2</sub> ( $\sim 1.5$ ) allow for submicron cross-section dimensions
- The evanescent field outside the core typically decays within 300nm, allowing for tight pitches of parallel waveguides
- Tight bending radius ( $< 5\mu\text{m}$ ) is possible, allowing for compact photonic integrated circuits

# TE & TM Polarization Modes

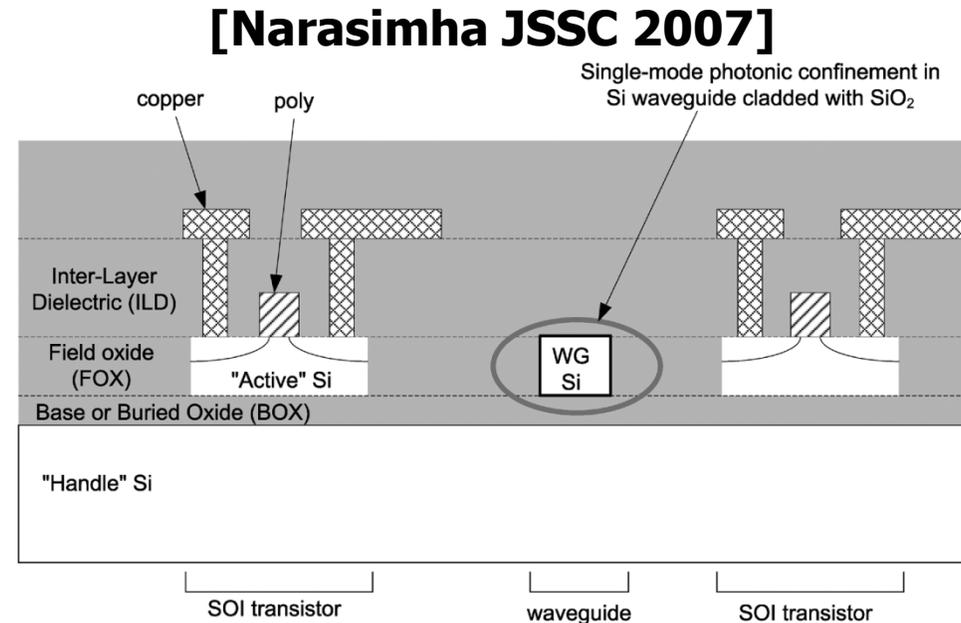
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**Figure 2.14** Field profiles for: (a) TE; (b) TM polarisation in a small strip silicon waveguide

- While on-chip silicon waveguides are most commonly single transversal mode, they generally support both TE and TM polarization modes
- Depending on the waveguide cross-section, these polarization modes can have different propagation constants. Although, PMD should be negligible for on-chip distances.
- TE modes have higher field intensity at the sidewalls, which are harder to keep smooth in the fabrication process
- This sidewall roughness results in typically higher loss for the TE mode

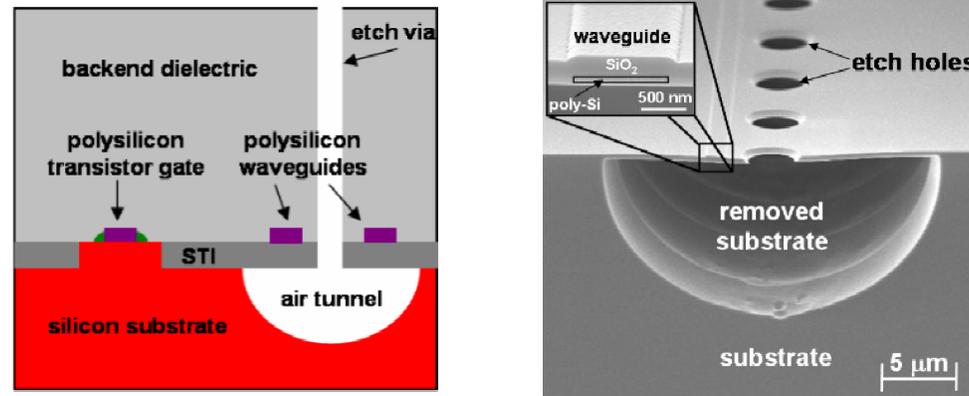
# CMOS Waveguides – SOI



- SOI processes have thicker buried oxide layers to sufficiently confine the optical mode
- Allows for relatively low-loss waveguides, with typical reported values of  $\sim 1\text{dB/cm}$

# CMOS Waveguides – Bulk CMOS

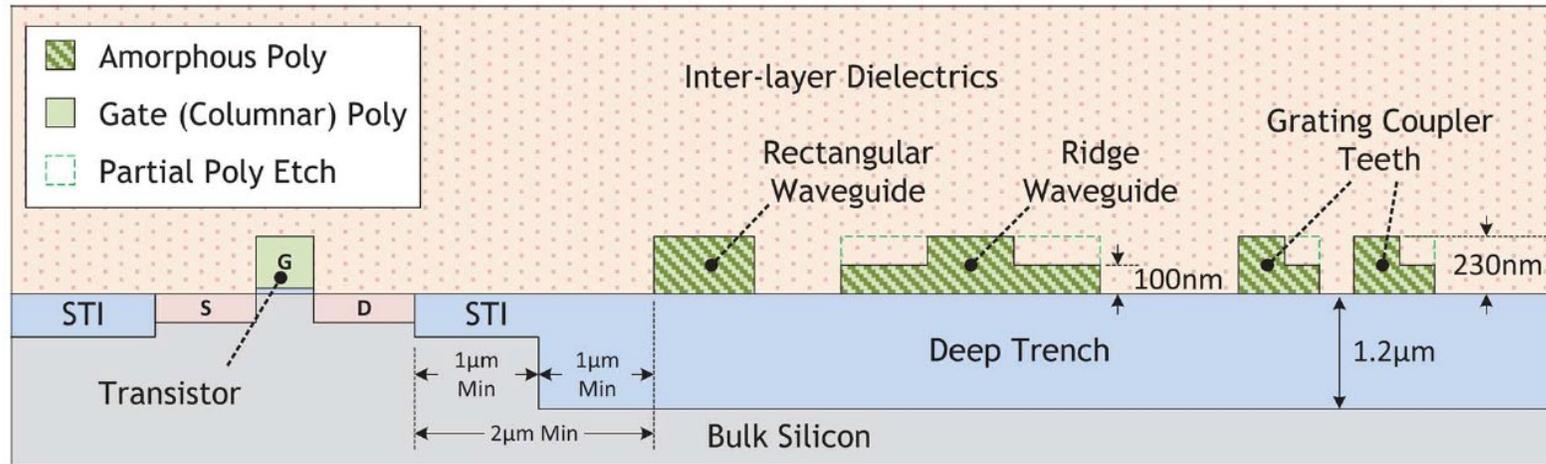
[Holzwarth CLEO 2008]



- Waveguides can be made in a bulk process with a polysilicon core surrounded by an  $\text{SiO}_2$  cladding
- However, thin STI layer means a significant portion of the optical mode will leak into the Si substrate, causing significant loss (1000dB/cm)
- Significant post-processing is required for reasonable loss (10dB/cm) waveguides in a bulk process

# CMOS Waveguides – Bulk CMOS

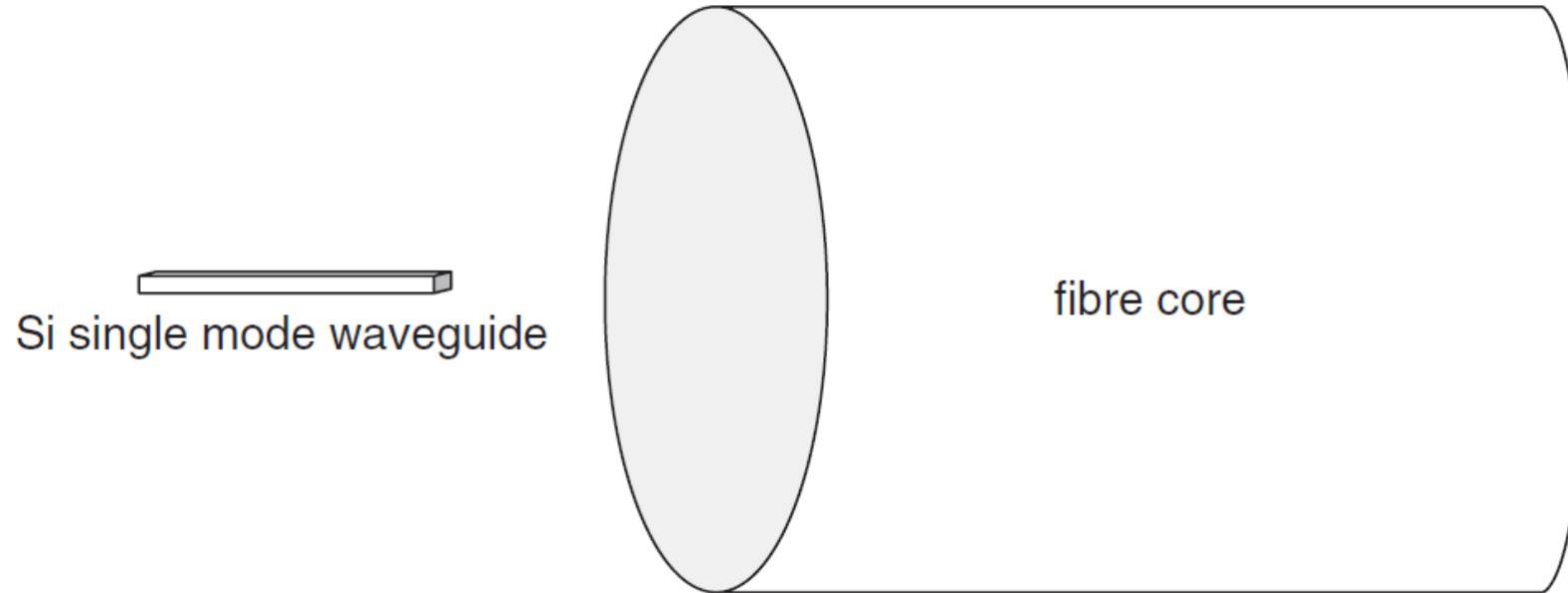
[Sun JSSC 2015]



- Introducing additional processing steps can also allow photonics in bulk CMOS
- Key step is the introduction of a deep-trench isolation oxide layer between the waveguides and the substrate
- Another partial polysilicon etch step allows for ridge waveguides and improved coupler design
- Reported loss is still close to 10dB/cm

# Coupling In & Out of the Chip

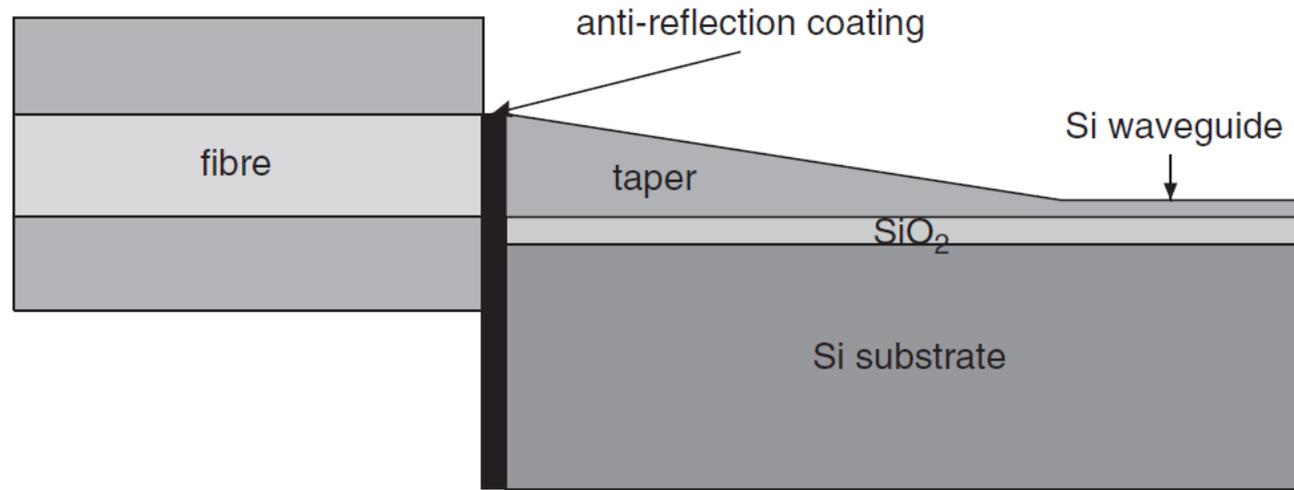
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- Butt or edge coupling of small silicon waveguides is inefficient, with  $\sim 20\text{dB}$  of loss common
- Thus, efficient mode converters or couplers are necessary

# Vertically-Tapered Waveguide

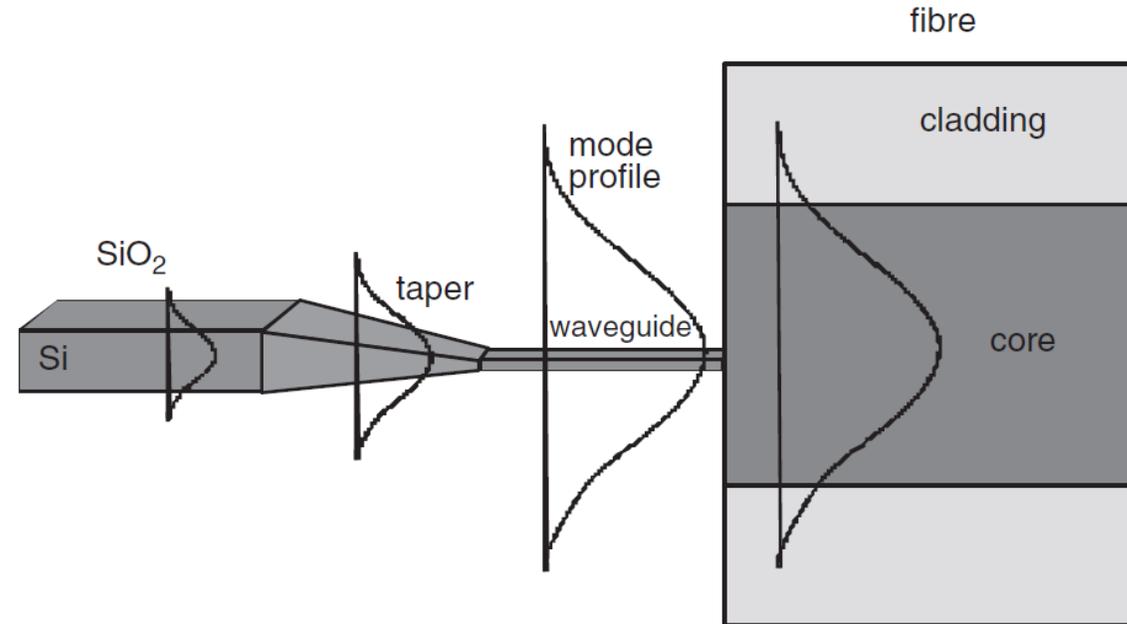
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- Waveguide height is increased near the edge of the chip to create an adiabatic taper
- Ideally, this transforms the fiber mode to the waveguide mode
- Reported losses are near 3dB

# Inverted-Tapered Waveguide

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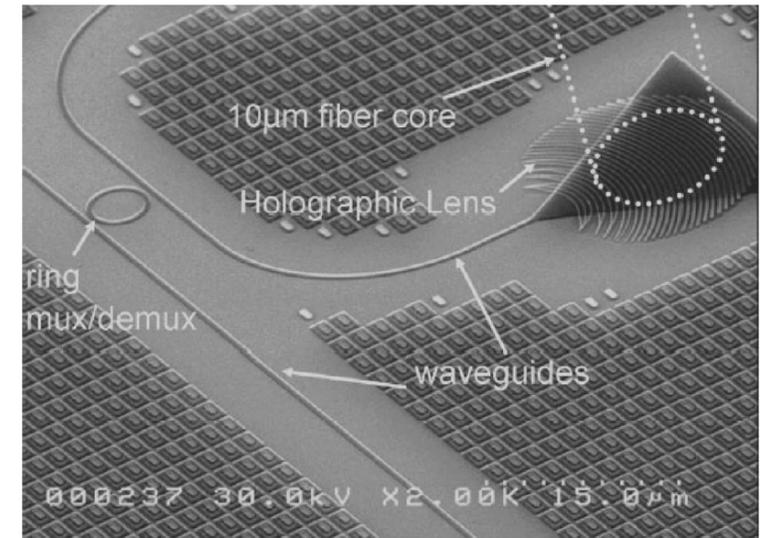


- Tapering the waveguide height down can cause the mode to become delocalized from the waveguide core and better match the fiber core
- Can actually achieve better coupling, with better than 1dB loss reported

# Surface Grating Couplers

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- Surface grating couplers are often more convenient for systems
- Here the fiber is brought in at a specific angle and the vertical light is coupled into the horizontal waveguide
- Loss of 1-1.5dB has been reported for over a 20nm (1537-1557nm) range



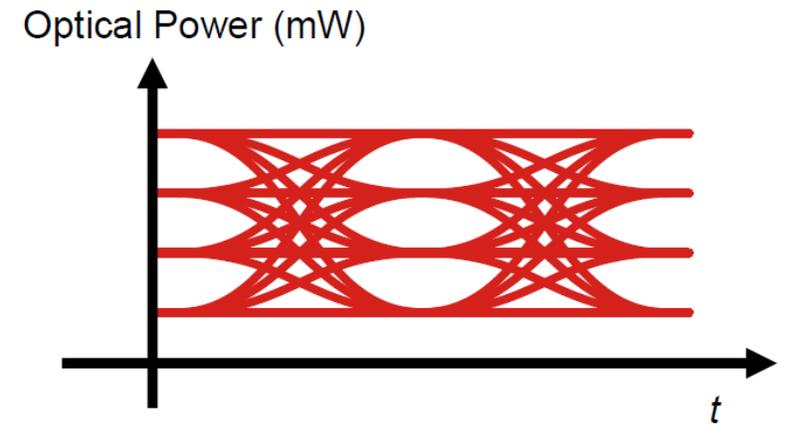
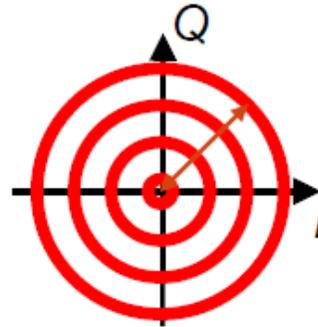
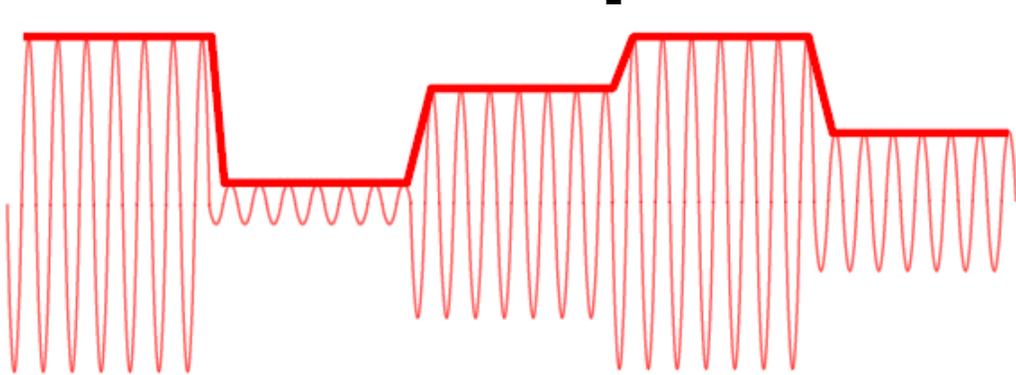
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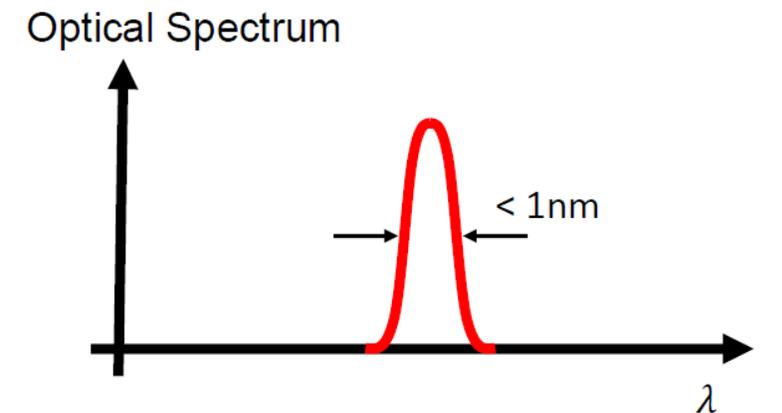
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# Intensity Modulation Direct Detection (IMDD)

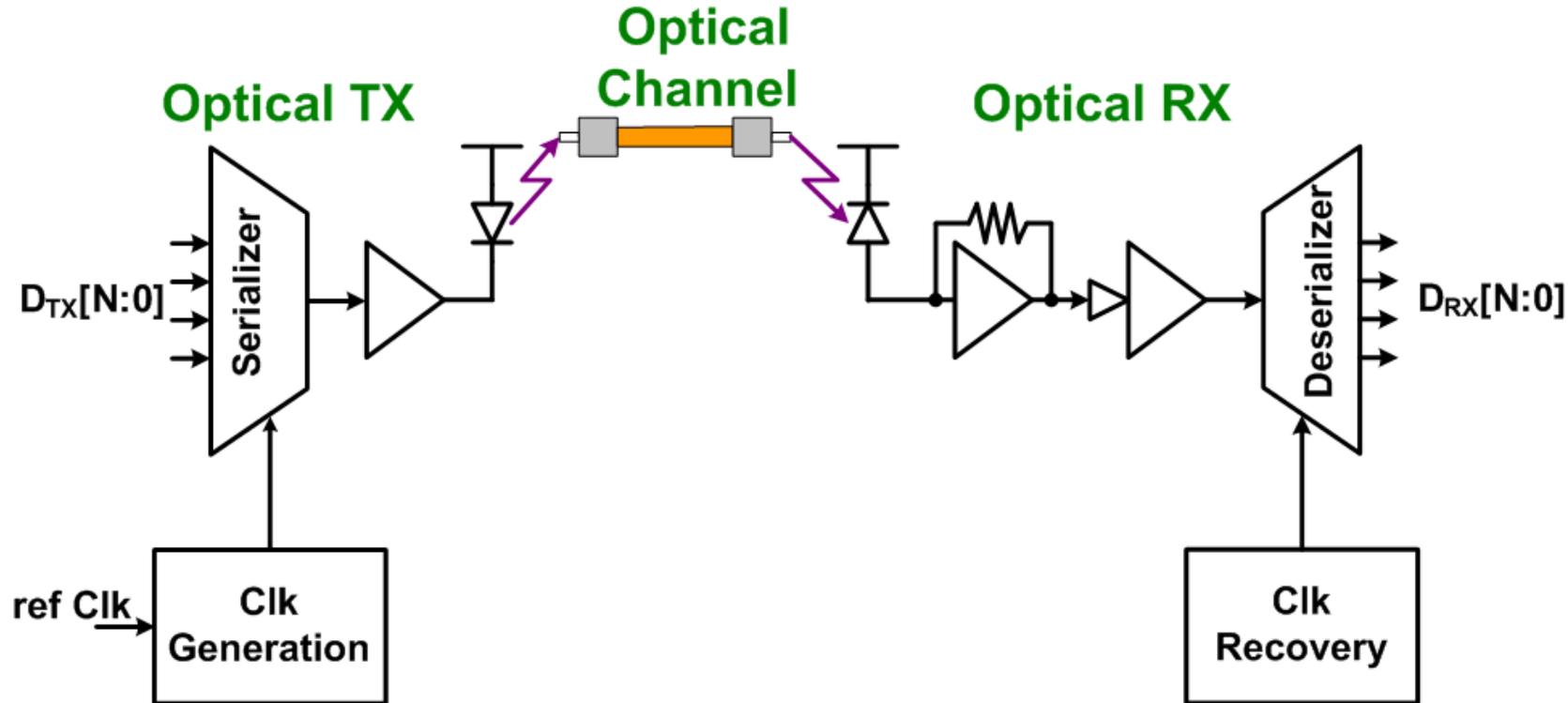
[Chan Carusone VLSI 2023]



- Symbols modulated in optical “intensity”,  $|E|^2$ , and the receiver “directly detects” this intensity/power level
- Effectively doing amplitude modulation on the optical carrier (1550nm = 194THz)
- Optical bandwidth is proportional to the baud rate
  - 100GBd modulation would induce approximately 100GHz bandwidth around the optical carrier, or 0.8nm in the wavelength domain



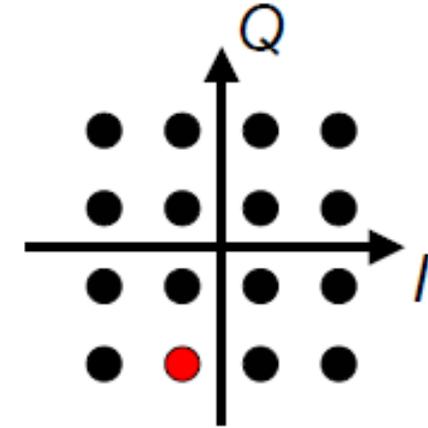
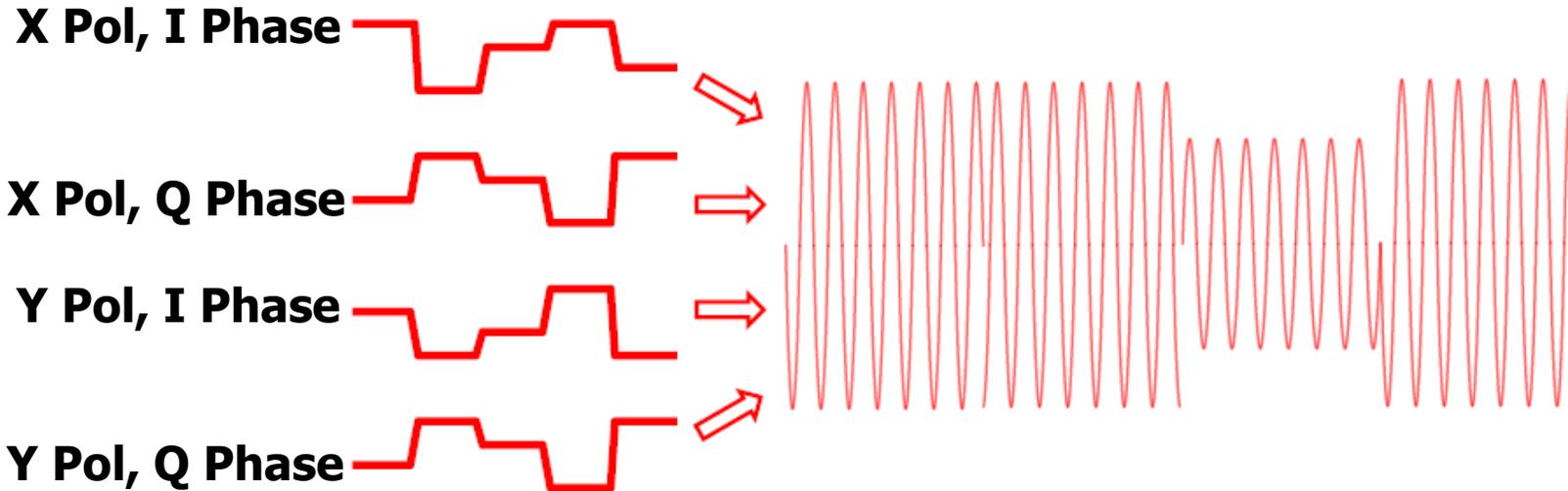
# Simple IMDD Transceiver



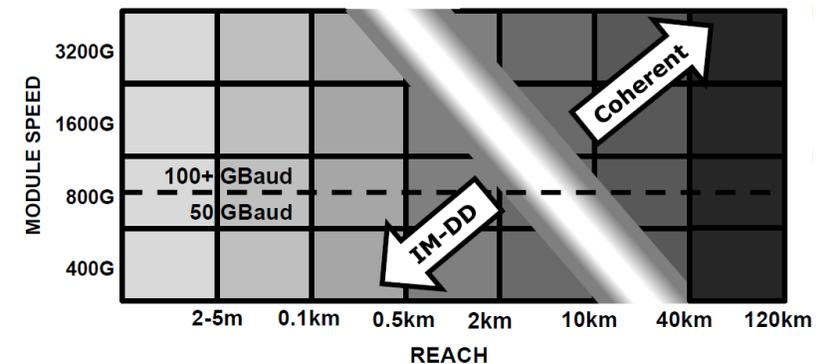
- The signal is transmitted with the optical carrier power either directly modulated with a single laser or externally modulated with a single optical modulator
- At the receiver, a single photodiode acts as a “square-law” detector and detects the incoming signal intensity/power and converts this to a photocurrent
  - Power of the photocurrent is proportional to the square of the optical power

# Coherent Optical Communication

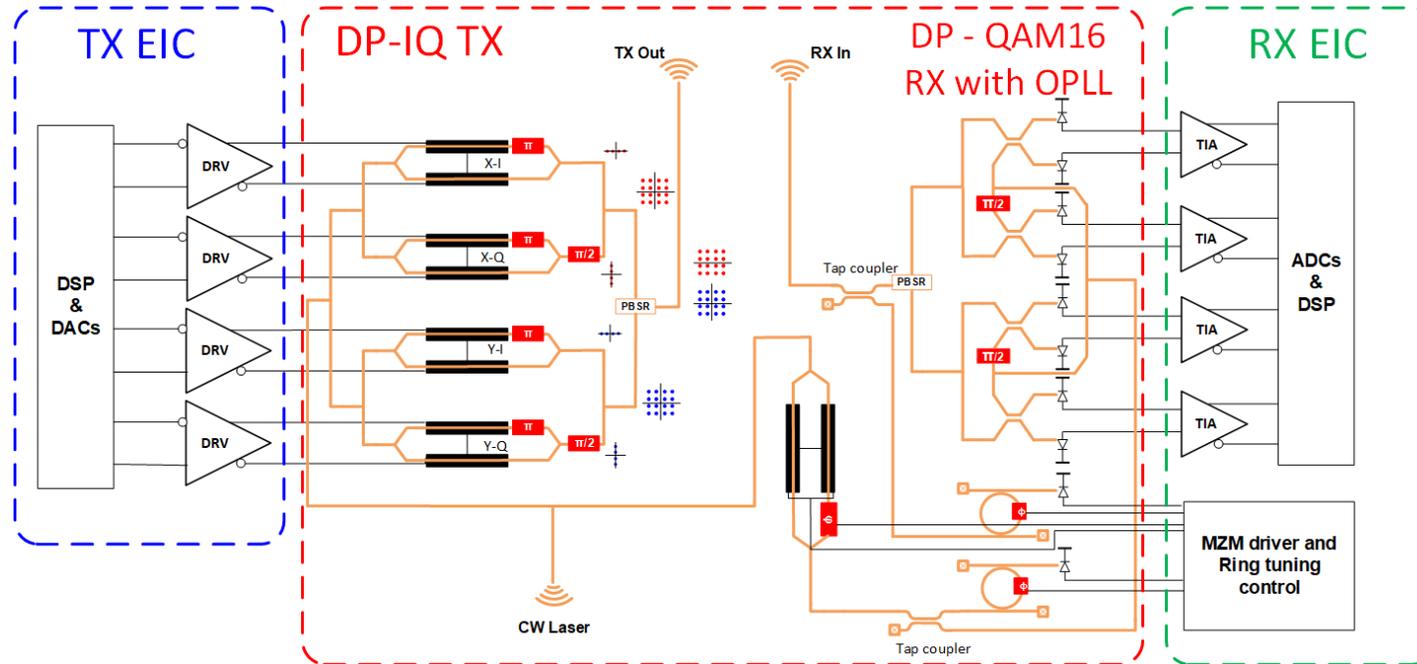
[Chan Carusone VLSI 2023]



- Symbol encoded in optical carrier power and phase
- Allows for 4 independent data streams on a single wavelength
  - I & Q phase
  - Dual polarization (X & Y)



# Dual-Polarization Coherent Transceiver



- At the transmitter, 2 modulators perform I/Q signal up-conversion to the optical carrier for the 2 polarizations
  - 4 total modulators
- At the receiver, the signal is down-converted with an optical hybrid and balanced photodetectors
- Phase must be tracked
  - Commonly done in the electrical DSP
  - Optical PLL offers the potential for lower-complexity “analog” coherent transceivers

# Outline

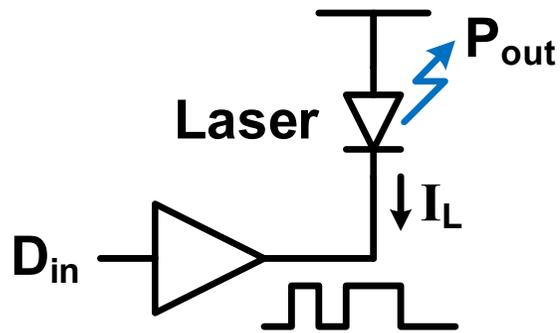
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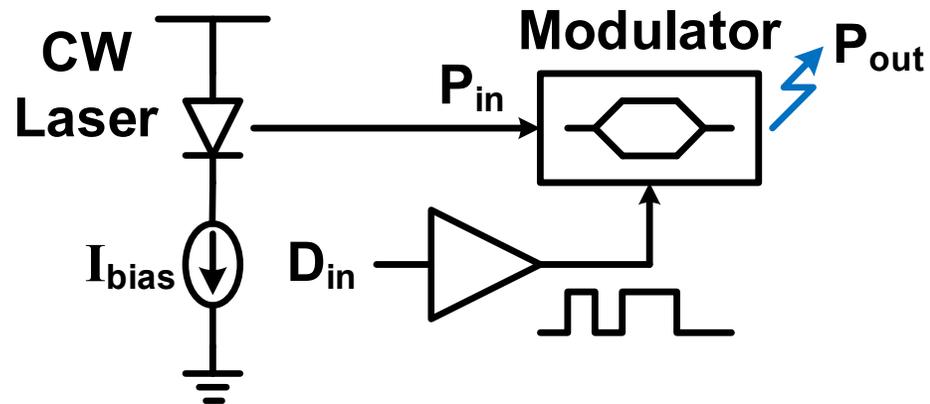
# Optical Modulation Techniques

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## Direct Modulation



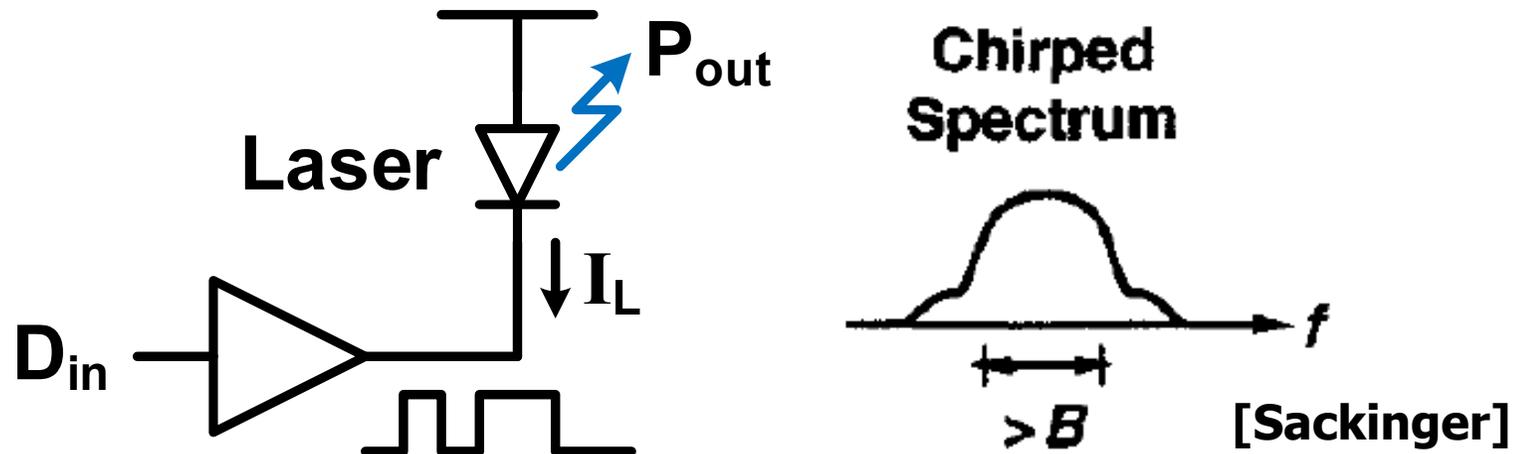
## External Modulation



- Two modulation techniques
  - Direct modulation of laser
  - External modulation of continuous-wave (CW) "DC" laser with absorptive or refractive modulators

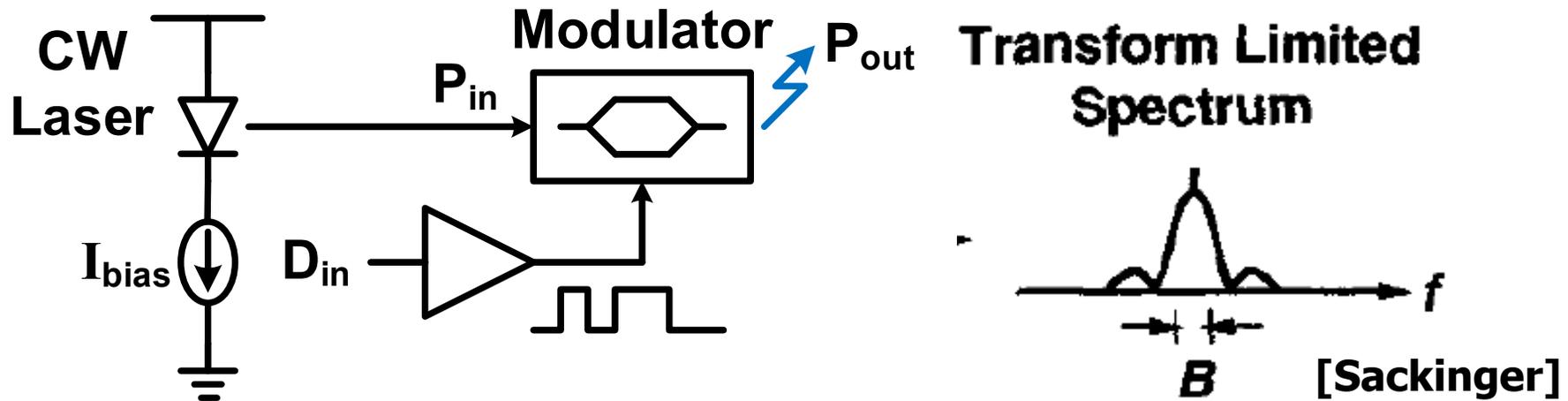
# Directly Modulated Laser

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- Directly modulating laser output power
- Simplest approach
- Introduces laser "chirp", which is unwanted frequency (wavelength) modulation
- This chirp causes unwanted pulse dispersion when passed through a long fiber

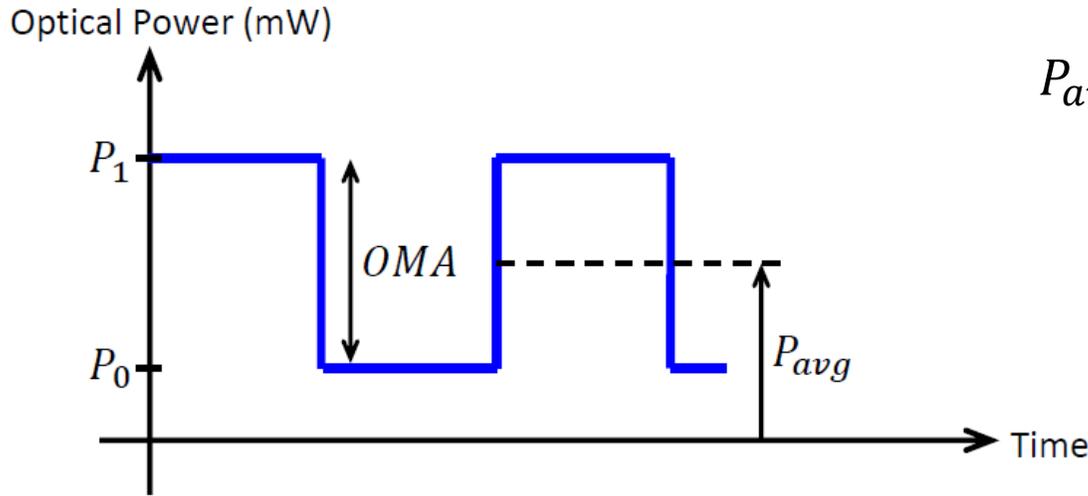
# Externally Modulated Laser



- External modulation of continuous-wave (CW) “DC” laser with absorptive or refractive modulators
  - Adds an extra component
  - Doesn’t add chirp, and allows for a transform limited spectrum

# Basic Definitions

[Webster CSICS 2015]



**Average Optical Power**

$$P_{avg} = \left( \frac{P_1 + P_0}{2} \right)$$

**Optical Modulation Amplitude**

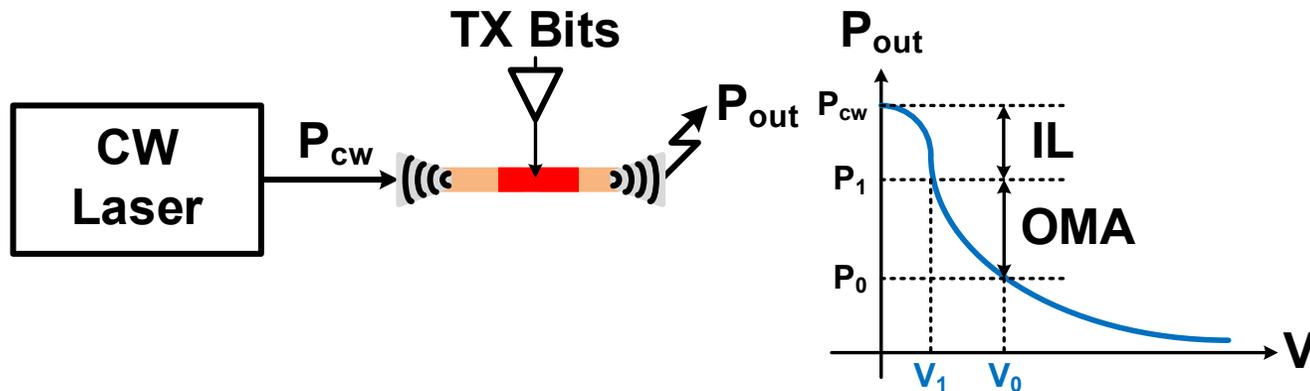
$$OMA = P_1 - P_0$$

**Extinction Ratio**

$$ER = \frac{P_1}{P_0}$$

$$OMA = 2P_{avg} \left( \frac{ER - 1}{ER + 1} \right) \quad P_{avg} = \frac{1}{2} OMA \left( \frac{ER + 1}{ER - 1} \right)$$

**EAM Transmission**



**Modulator OMA Penalty**

$$TP_{OMA} = \frac{P_{CW}}{P_1 - P_0} = \frac{P_{CW}}{OMA} = \frac{ER}{IL(ER - 1)}$$

# Transmitter and Dispersion Eye Closure Quaternary (TDECQ)

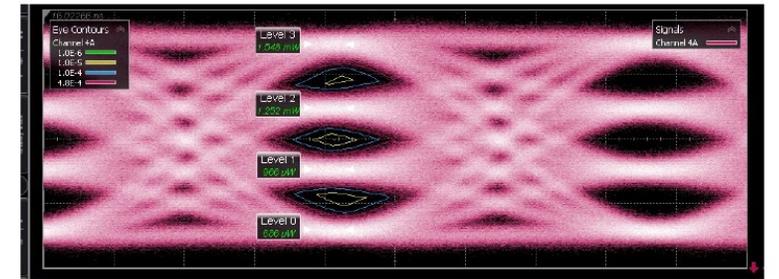
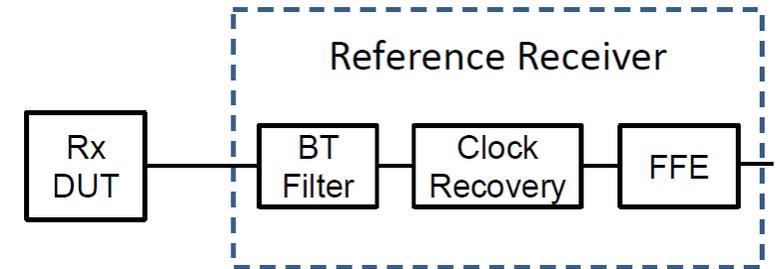
- Optical transmitter specification that captures the impact of TX nonidealities on RX OMA sensitivity
  - TX with 3dB TDECQ will require the RX OMA sensitivity to be 3dB better for the same SER

- Measured with a reference receiver consisting of a 4<sup>th</sup>-order Bessel-Thomson lowpass filter and 5-tap FFE

- Ideal PAM4 tolerable noise:  $\sigma_{ideal} = \frac{OMA}{2Q^{-1}(\frac{2}{3}SER_{target})}$

- Measurement calculates the actual noise that can be added to the TX to achieve the target SER, which will be less than  $\sigma_{ideal}$  due to nonidealities

## [Chan Carusone]



$$TDECQ = 10 \cdot \log_{10}\left(\frac{\sigma_{ideal}}{\sigma_R}\right)$$

- Typical spec: TDECQ < 2.4dB

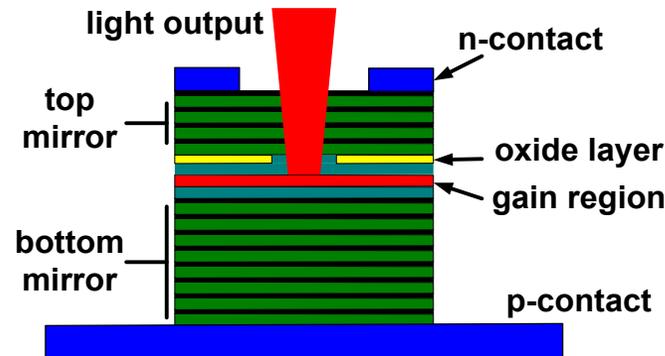
# Optical Transmitter Devices

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- Vertical-Cavity Surface-Emitting Laser (VCSEL)
- Electro-Absorption Modulator (EAM)
- Ring-Resonator Modulator (RRM)
- Mach-Zehnder Modulator (MZM)

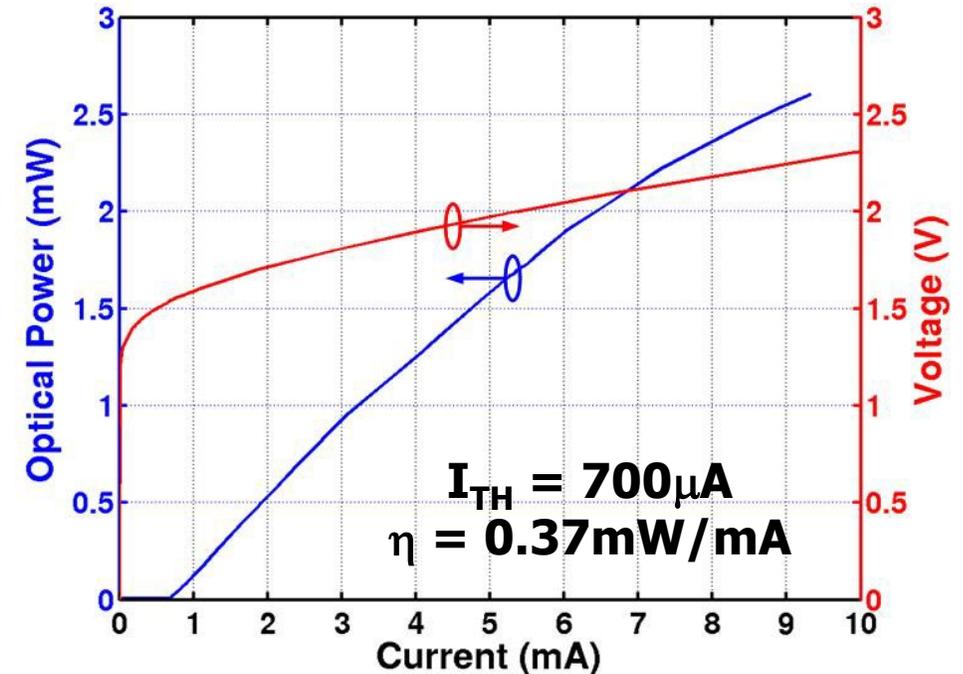
# Vertical-Cavity Surface-Emitting Laser (VCSEL)

## VCSEL Cross-Section



- VCSEL emits light perpendicular from top (or bottom) surface
- Important to always operate VCSEL above threshold current,  $I_{TH}$ , to prevent “turn-on delay” which results in ISI
- Operate at finite extinction ratio ( $P_1/P_0$ )

## VCSEL L-I-V Curves



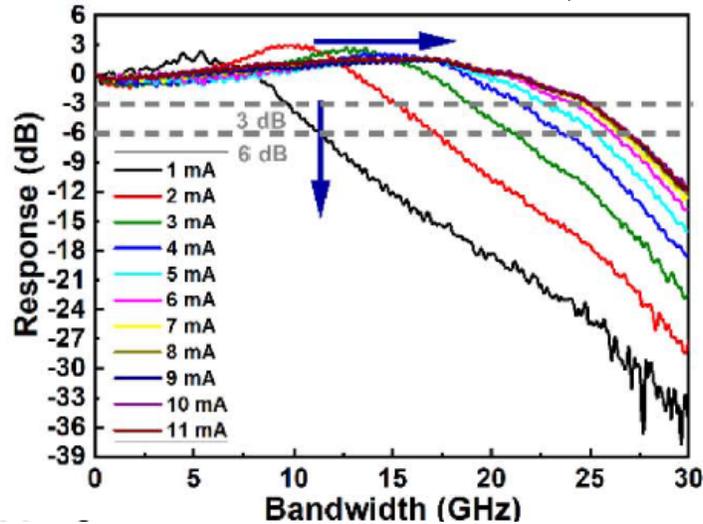
$$P_o = \eta(I - I_{TH})$$

$$\text{Slope Efficiency } \eta = \frac{\Delta P}{\Delta I} \left( \frac{\text{W}}{\text{A}} \right)$$

# VCSEL Bias-Dependent Bandwidth

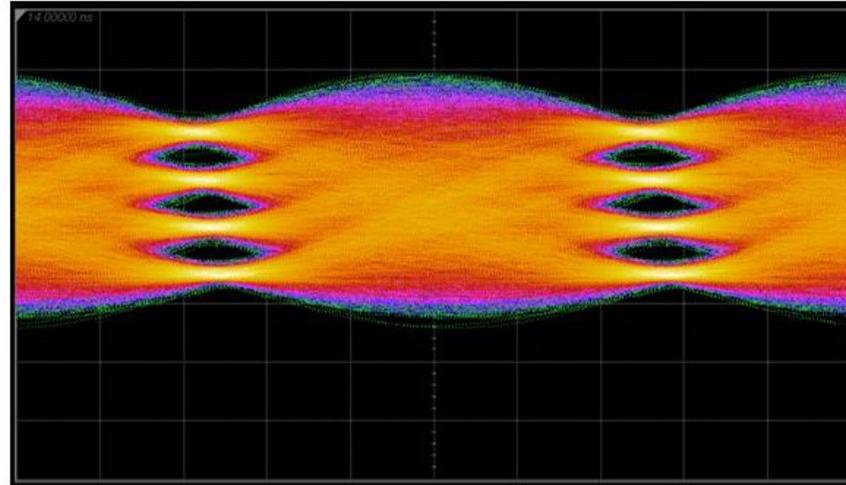
[Wu PhRes 2024]

$$BW \propto \sqrt{I_{avg} - I_{TH}}$$



200Gb/s 850nm MM-VCSEL  
(c) 9mA, 50m (EMB 7500 MHz.km)

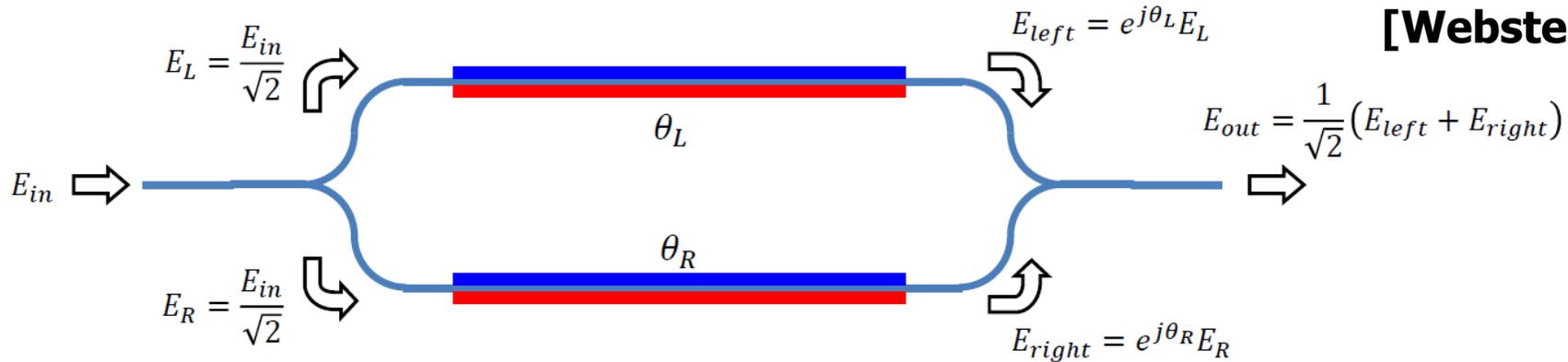
[Wang PhWest 2025]



- 9mA bias
- 7-tap TX FIR
- 2.2dB ER
- 50m enhanced MMF
- 25-tap FFE at scope (RX)

- VCSEL electrical impedance and rate equations cause bias-dependent bandwidth
  - State of the art is 39GHz at 9mA bias [Wang PhWest 2025]
- Lower bias results in an underdamped low-bandwidth response
- Driving the VCSELs significantly above threshold reduces ER and results in a speed/power tradeoff
- 200Gb/s PAM4 demonstrated

# Mach-Zehnder Modulator (MZM)



- An optical interferometer is formed with the incoming light split, experiencing phase shifts through the two paths, and then recombined
- Assuming no loss and a perfect 50/50 splitter/combiner

$$\Delta\phi = \frac{(\theta_R - \theta_L)}{2}$$

$$\phi = \frac{(\theta_R + \theta_L)}{2}$$

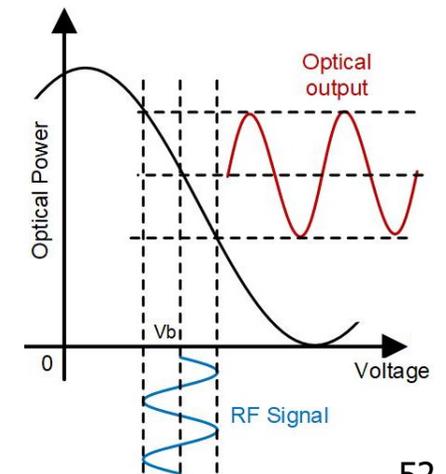
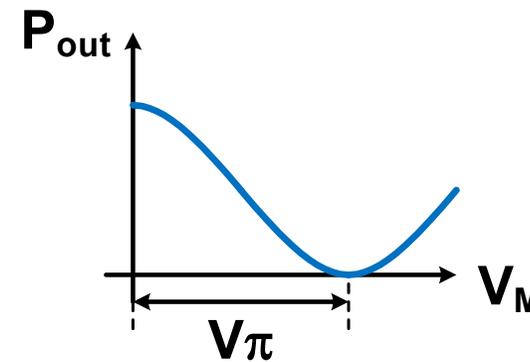
Field Response

$$E_{out} = E_{in} \cos(\Delta\phi) e^{j\phi}$$

Intensity Response

$$P_{out} = |E_{out}|^2 = \frac{1}{2} |E_{in}|^2 [1 + \cos(\theta_R - \theta_L)]$$

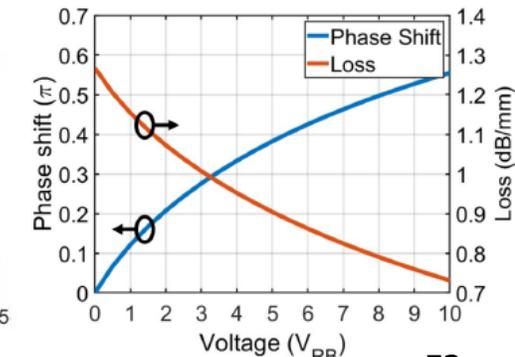
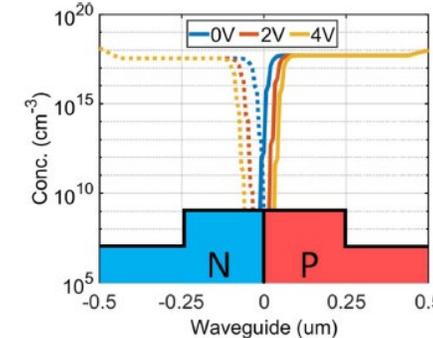
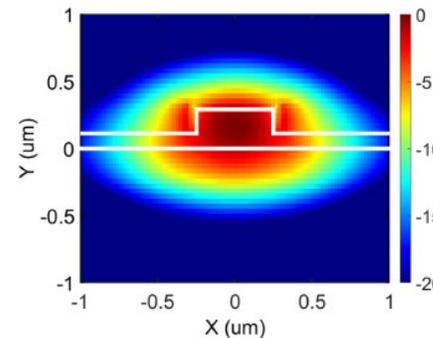
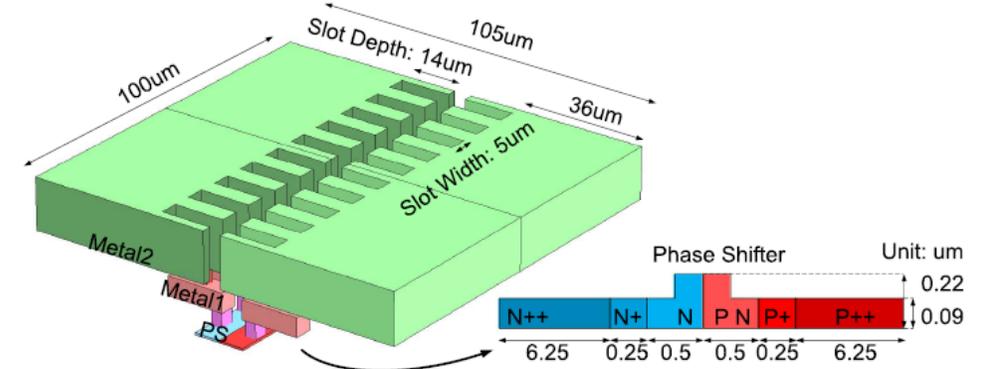
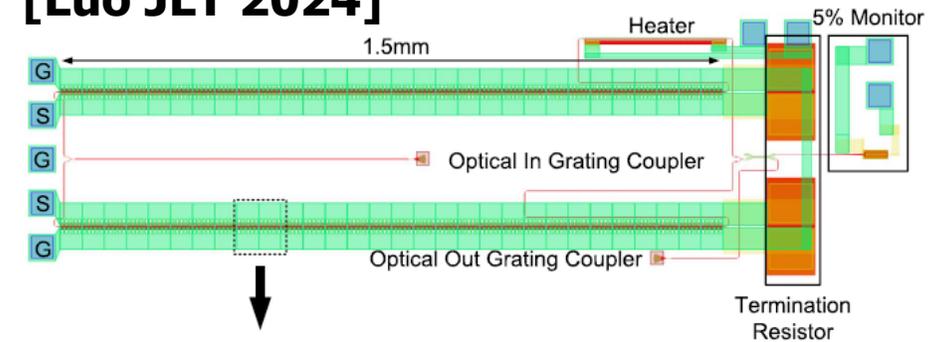
$$\frac{P_{out}}{P_{in}} = \frac{1}{2} [1 + \cos(\theta_R - \theta_L)] = \frac{1}{2} \left[ 1 + \cos\left(\pi \cdot \frac{V_M}{V_\pi}\right) \right]$$



# Silicon Photonic MZMs

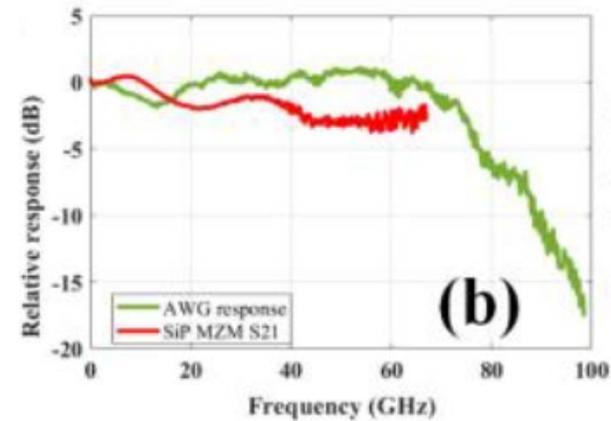
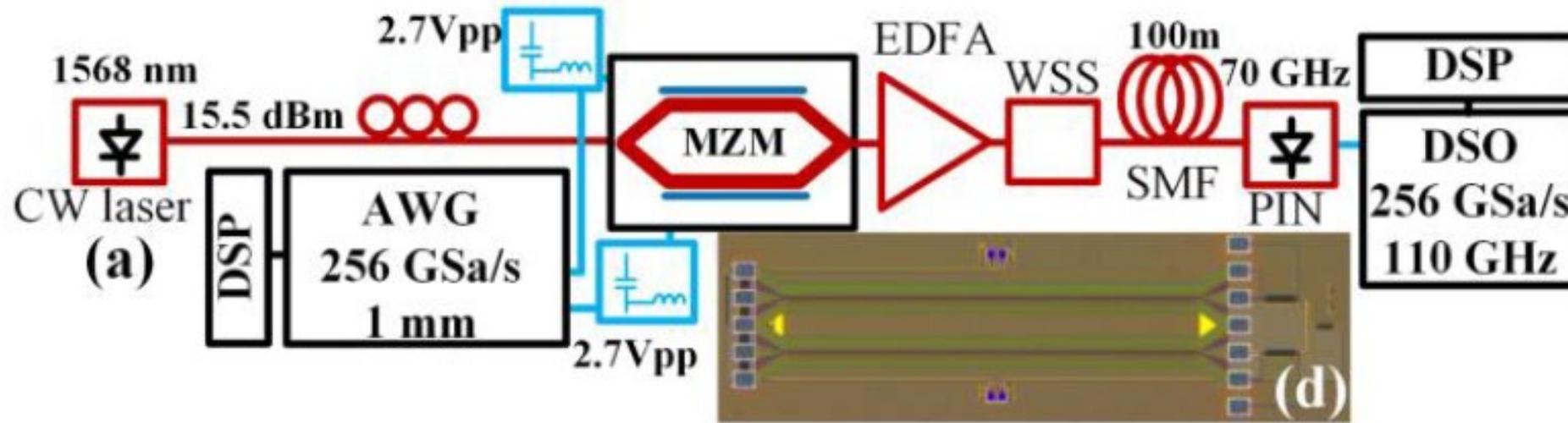
- Silicon waveguide is doped as a PN junction with the depletion region modulated as a function of the applied reverse bias voltage
- The resultant change in carrier density within the depletion region causes the refractive index to change through the plasma dispersion effect
- Tradeoffs in  $V_{\Pi}$ , bandwidth, and loss
- Typical values
  - $V_{\Pi}L = 1.5\text{-}2\text{V}\cdot\text{cm}$
  - $V_{\Pi} = 6\text{-}7\text{V}$
  - $\text{BW} = 30\text{-}35\text{GHz}$
- Results in mm-scale devices typically driven in a traveling-wave manner

[Luo JLT 2024]



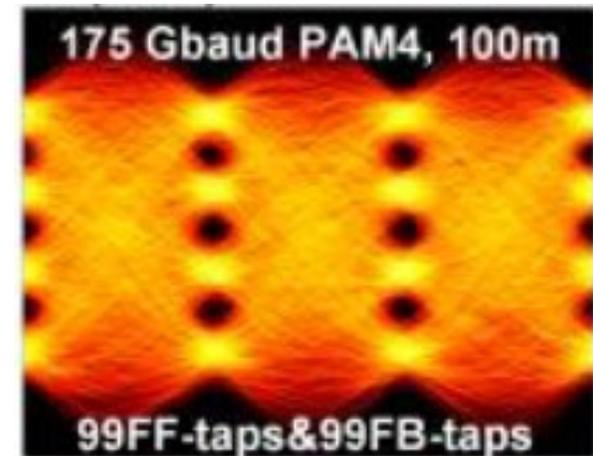
# 42GHz Silicon Photonic MZM

[Ostrovskis OFC 2025]



- 42GHz bandwidth with 2.5V bias
- $V_{\pi}L = 1.7V \cdot cm$
- $L=1.5mm$
- 3.6dB insertion loss plus 2.5dB per grating coupler
- 350Gb/s PAM4 operation achieved with scope (RX) equalization of 99-tap FFE and 99-tap DFE

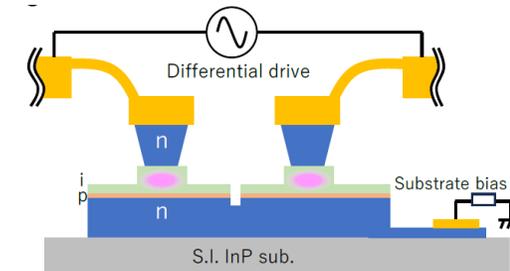
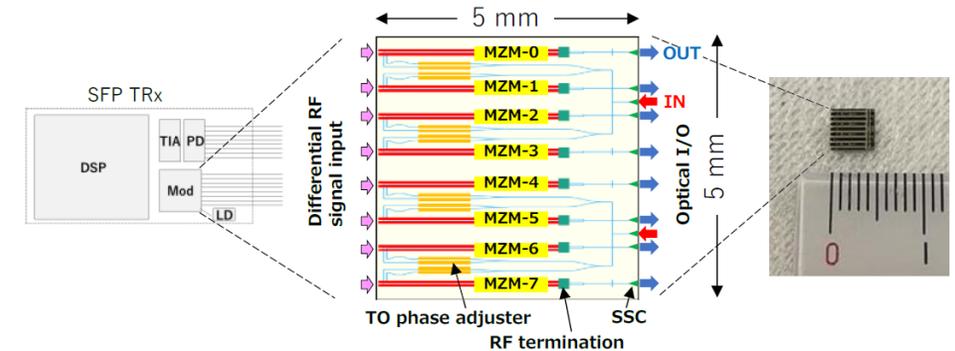
**350Gb/s PAM4**



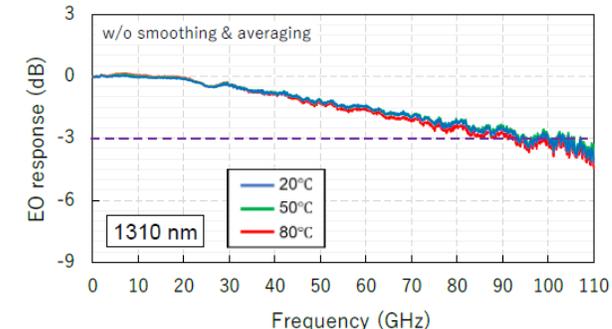
# InP MZMs

- InP MZMs are commonly used for long-reach transmission due to small  $V_{\Pi}$ , high bandwidth, and low chirp
- Comparable with differential drive
- InP is generally an expensive material
- State of the art is 100GHz bandwidth that achieved 430Gb/s PAM6
  - 65 $\Omega$  differential impedance
  - Mismatch with 100 $\Omega$  AWG required a 4001 tap T/2-spaced FFE
  - RX DSP used 61-tap T/2-spaced FFE

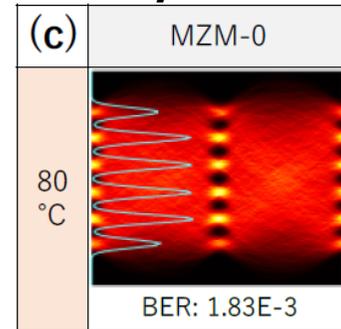
## [Ogiso OFC 2025] 8-Channel Module



## 100GHz Bandwidth

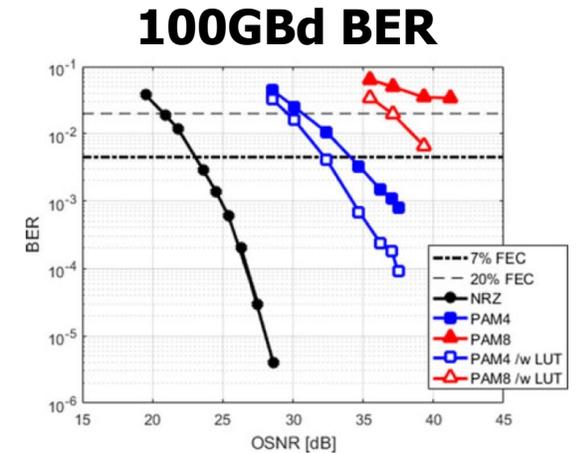
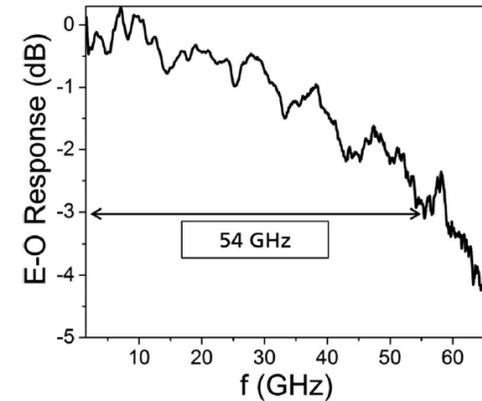
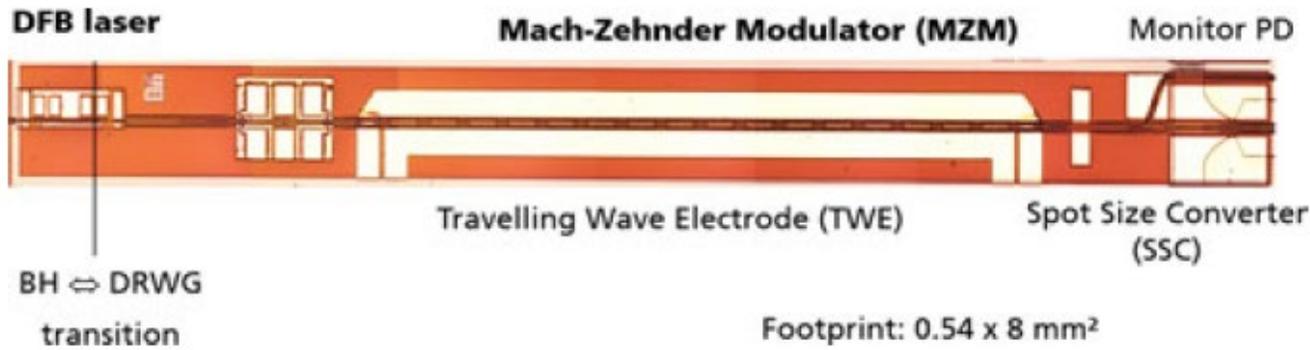


## 430Gb/s PAM6



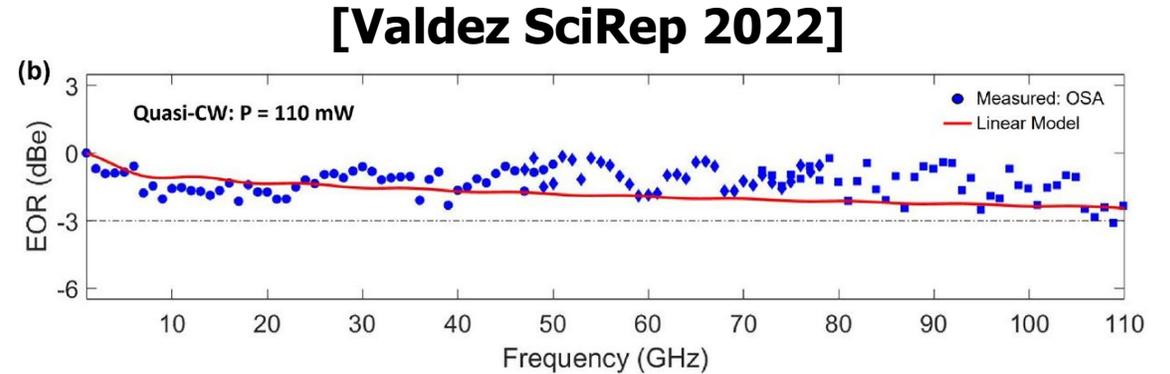
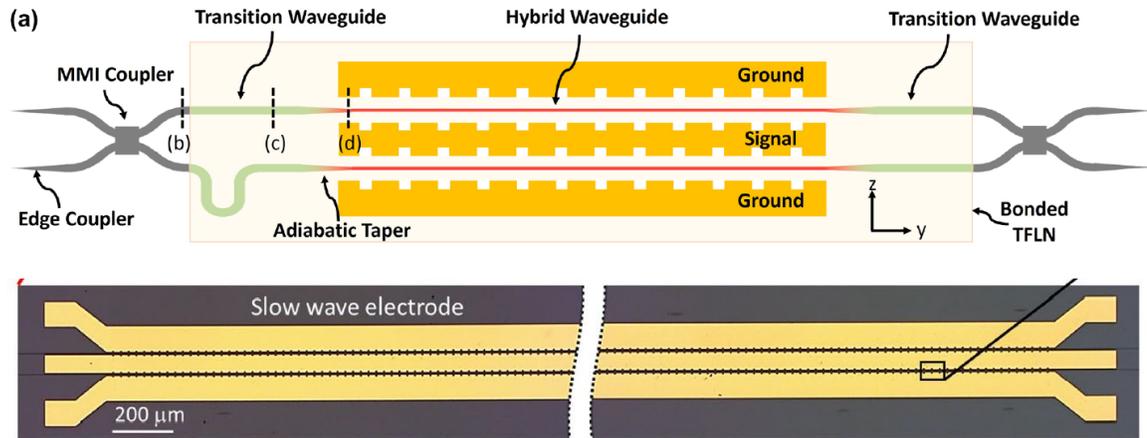
# InP Monolithic DFB Laser + MZM

[Lange JLT 2018]

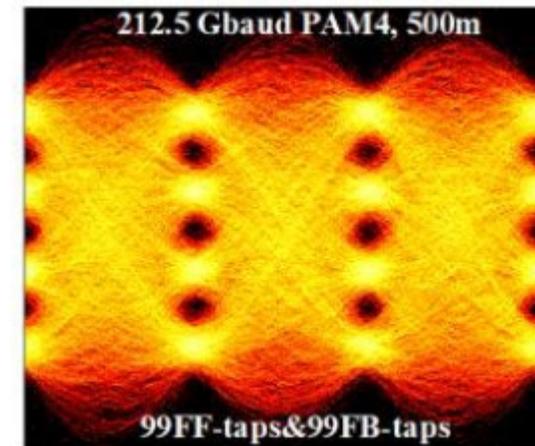
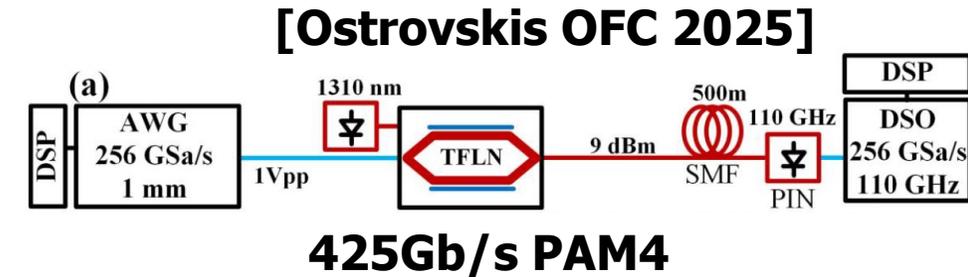


- InP platform allows for monolithic DFB laser and MZM integration
- MZM parameters
  - 54GHz bandwidth
  - $V_{\Pi} = 2V$
  - $V_{\Pi}L = 0.55V \cdot cm$
- 200Gb/s PAM4 operation achieved with 7% FEC
- 300Gb/s PAM8 possible with 20% FEC and LUT-based equalizer

# Thin-Film Lithium Niobate (TFLN) MZM

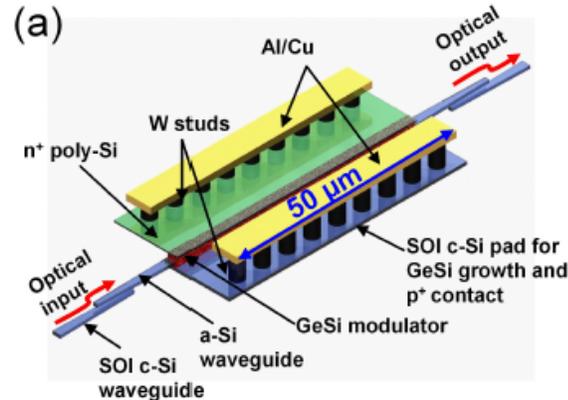


- Low loss and high bandwidth allow for longer modulators with low  $V_{\Pi}$  values
- 110GHz MZM realized by bonding LN on Si waveguides
  - Potential to leverage existing SiP platforms
  - $V_{\Pi}L = 3.1V \cdot cm$
  - $L=5mm$
  - 1.8dB insertion loss
- 425Gb/s PAM4 demonstrated with similar device

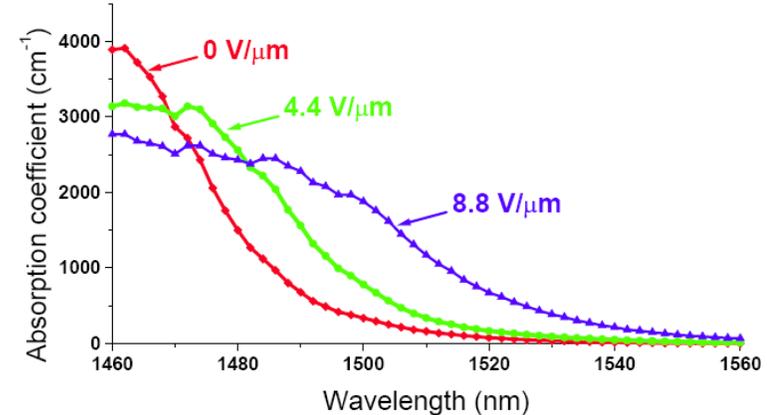


# Electro-Absorption Modulator (EAM)

Waveguide EAM [Liu 2008]



[Helman JSTQE 2005]

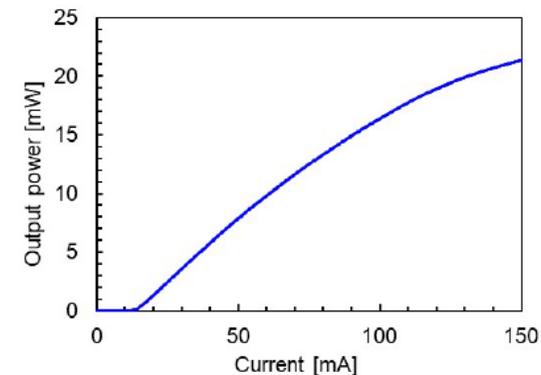
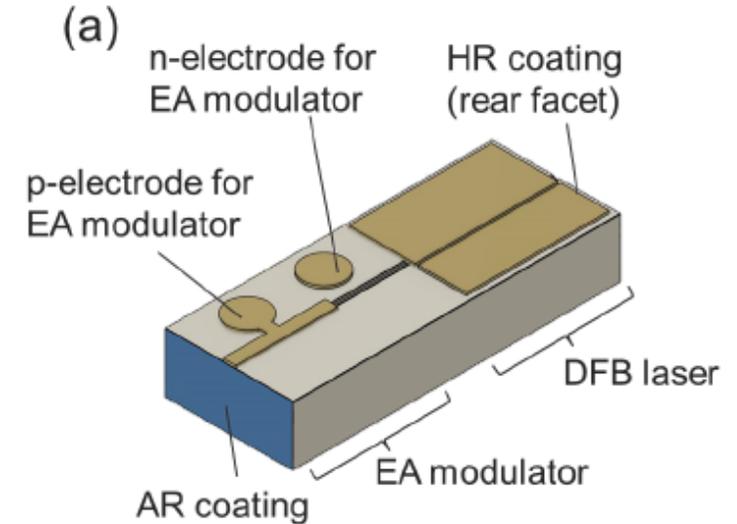


- Electro-absorption modulators operate with voltage-dependent absorption of light passing through the device
- The device structure is a reverse-biased p-i-n diode
- The Franz-Keldysh effect describes how the effective bandgap of the semiconductor decreases with increasing electric field, shifting the absorption edge
- While this effect is weak, it can be enhanced with device structures with multiple quantum wells (MQW) through the quantum-confined Stark effect

# Monolithic DFB Laser + EAM (EA-DFB)

- InP platform allows for monolithic DFB laser and EAM integration
- DFB laser operates in forward bias and the EAM is in reverse bias
- 226Gb/s PAM4 operation achieved with 15-tap TX FFE
  - Semi-insulating substrate allows for 4 independent electrodes, 2 for DFB and 2 for EAM
  - Allows for differential drive of EAM
  - 5.1dB extinction ratio with  $2V_{ppd}$  swing

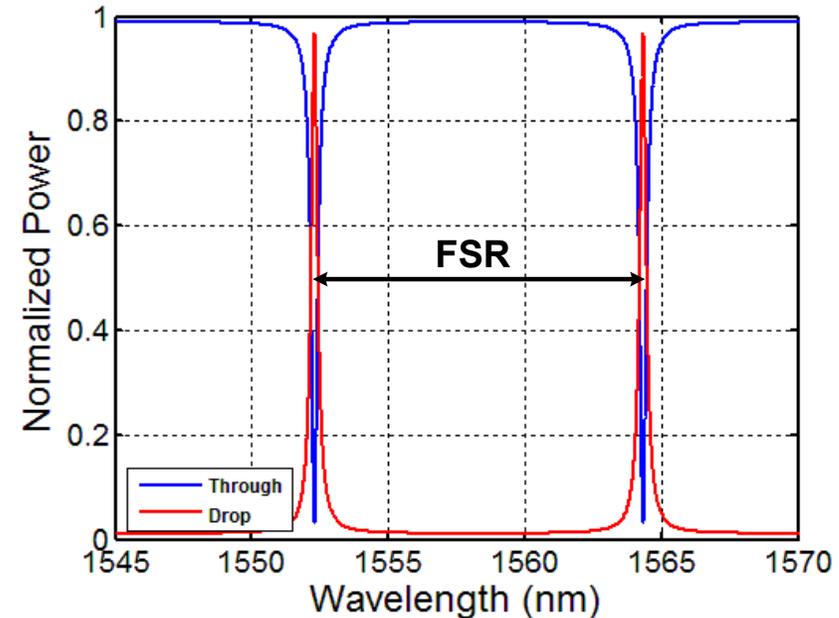
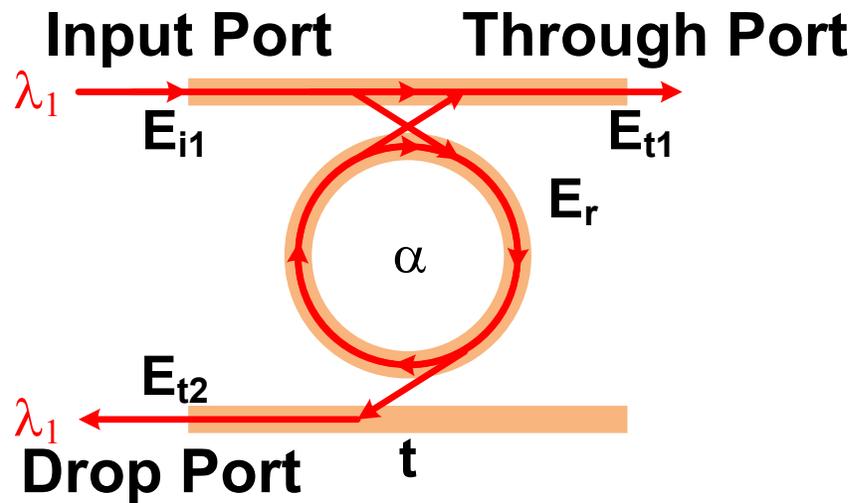
[Ohno OFC 2025]



**226Gb/s PAM4**

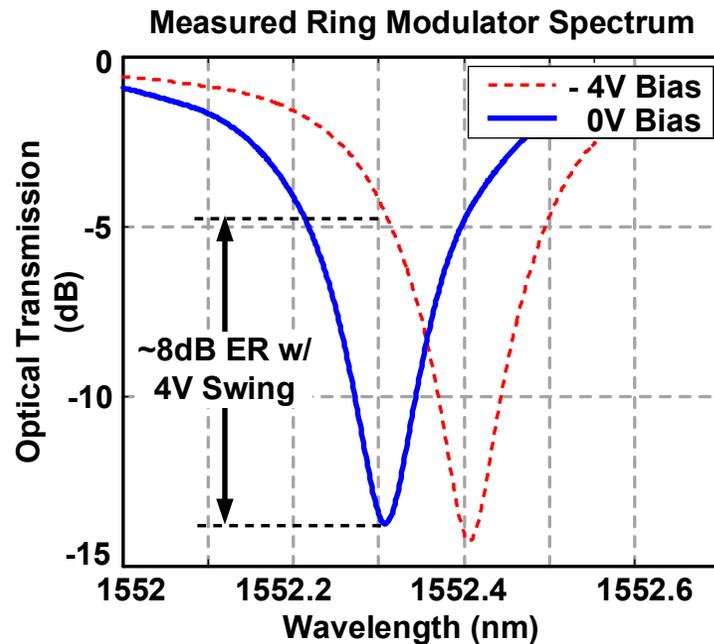
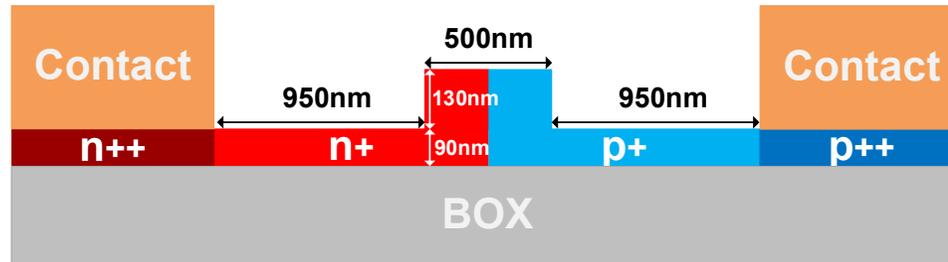
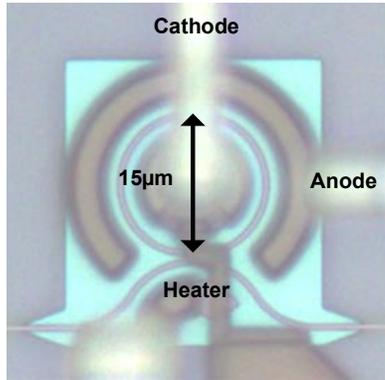
Fiber length	BTB
OuterER [dB]	4.8
TDECQ [dB]	2.13
Waveform with 15-tap FFE	

# Ring Resonator Filter



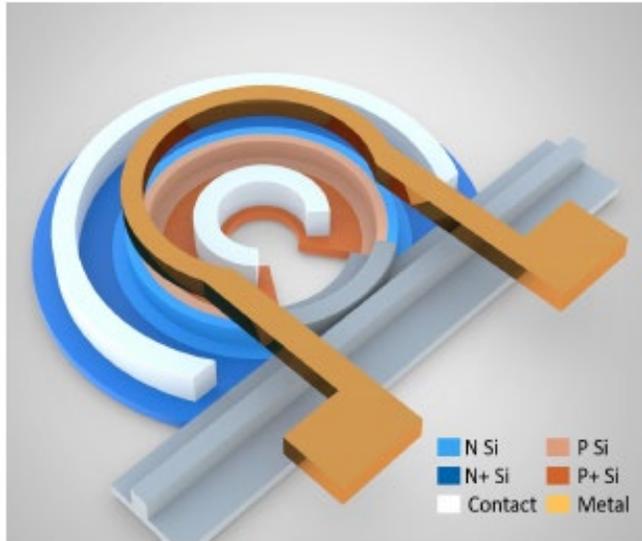
- Ring resonators display a high- $Q$  notch filter response at the through port and a band-pass response at the drop port
- This response repeats over a free spectral range (FSR)

# Carrier-Depletion Ring Modulator

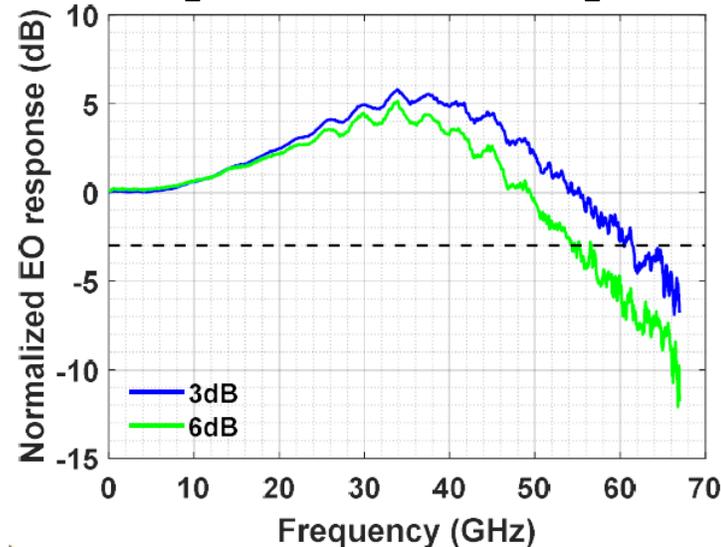


	ISSCC 2013	ISSCC 2015
Ring Type	Injection	Depletion
Doping Profile	PIN	Lateral PN
Q	8000	5000
Tunability (pm/V)	350	25
Data Rate	9Gb/s	25Gb/s
Swing for >7dB ER	< 2V <sub>pp</sub>	> 4V <sub>pp</sub>

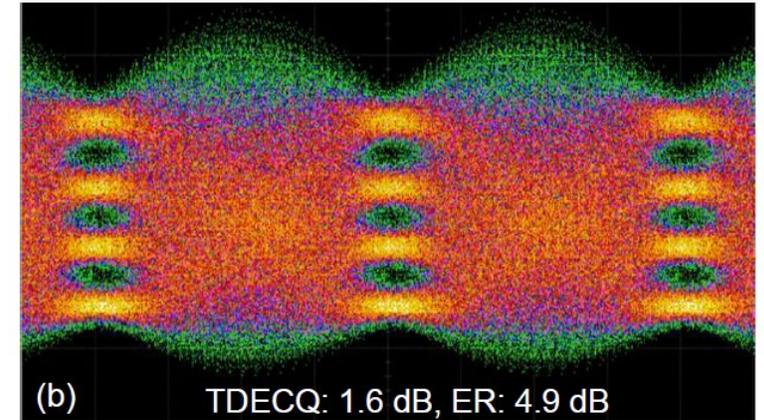
# 240Gb/s PAM4 RRM



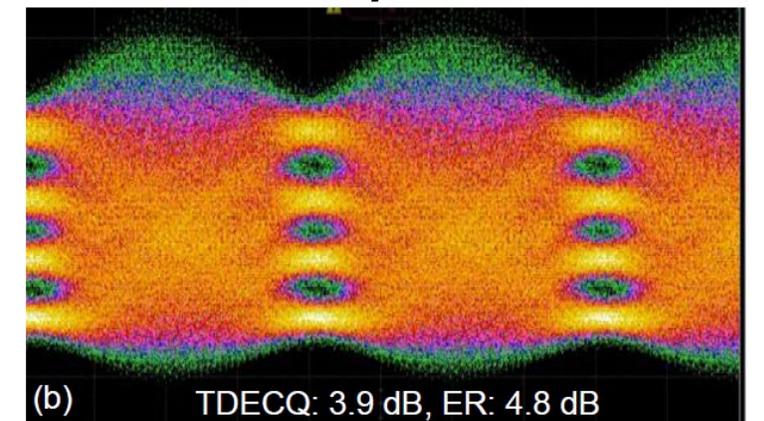
[Sakib OFC 2022]



224Gb/s PAM4



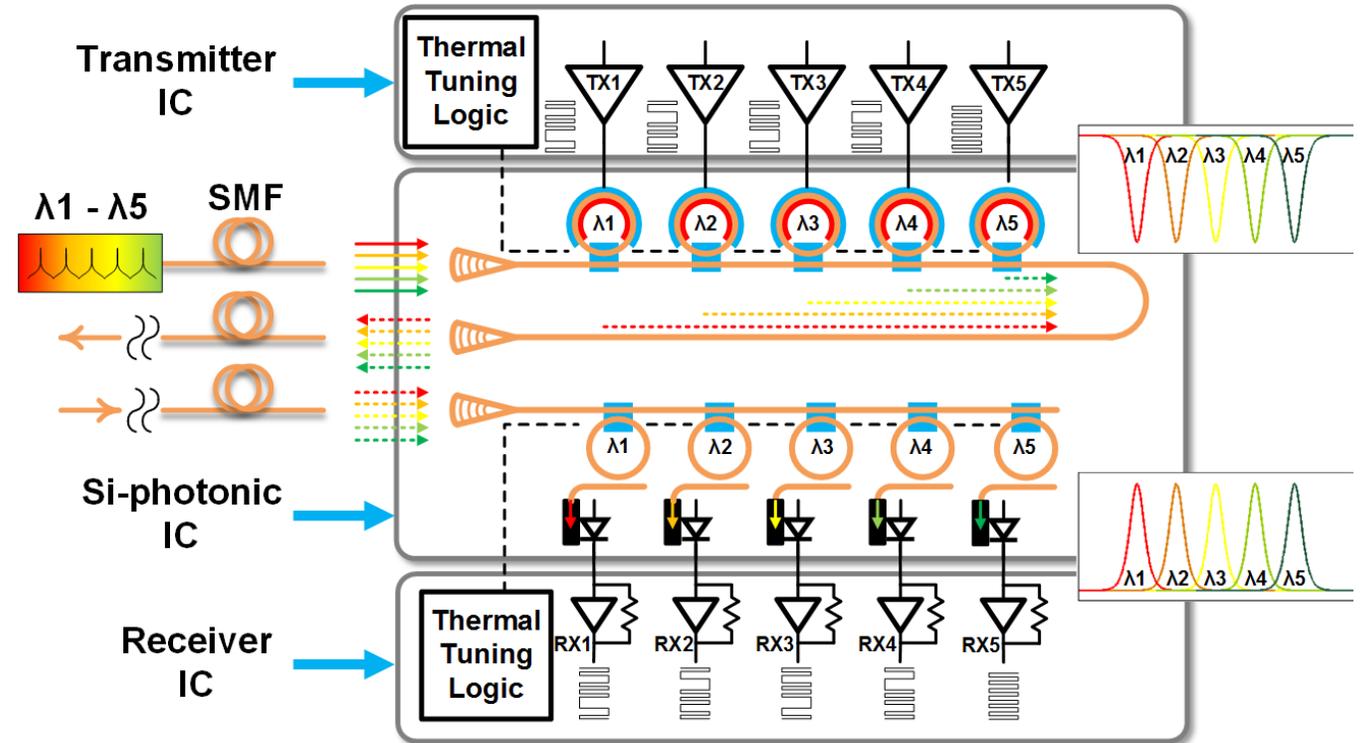
240Gb/s PAM4



- 4mm radius ring for reduced capacitance and 16.3nm FSR
  - Capable of supporting 12 DWDM channels with 200GHz spacing
- $Q=4000$
- Intrinsic RC bandwidth of 100GHz

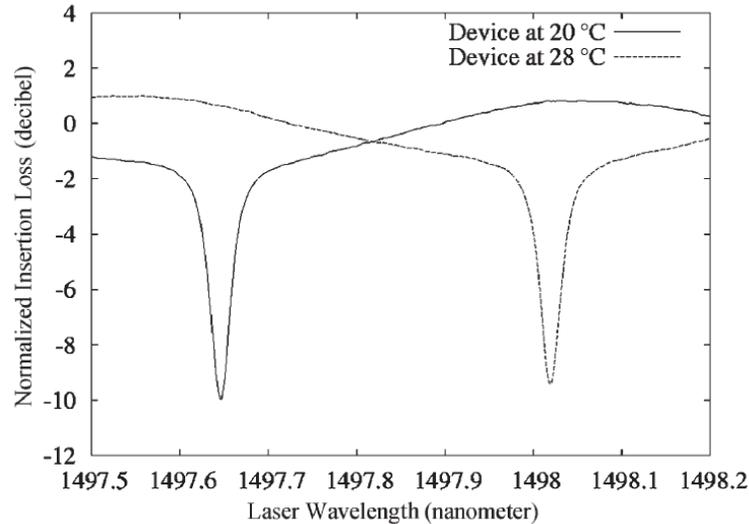
# Wavelength Division Multiplexing w/ Ring Resonators

- Ring resonators can act as both modulators and add/drop filters to steer light to receivers or switch light to different waveguides
- Potential to pack >30 waveguides, each modulated at more than 10Gb/s on a single on-chip waveguide

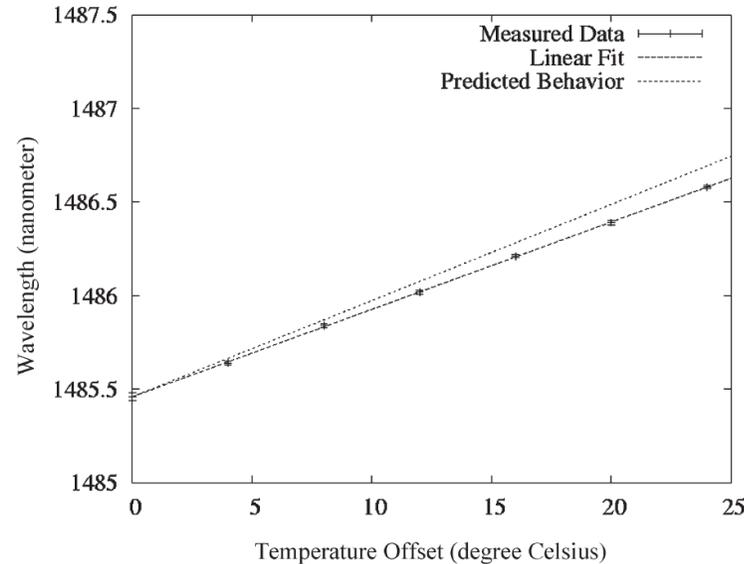


# RRM Thermal Sensitivity

$$dn_{\text{eff}} = \left( \frac{\partial n_{\text{eff}}}{\partial \epsilon_c} \right) \left( \frac{\partial \epsilon_c}{\partial T} \right) dT + \left( \frac{\partial n_{\text{eff}}}{\partial \lambda} \right) d\lambda.$$

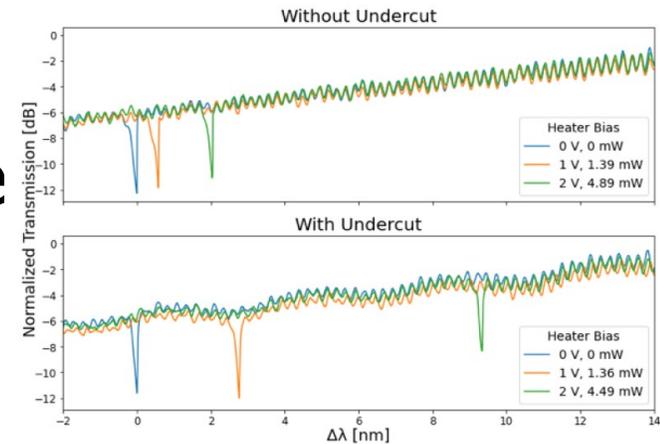
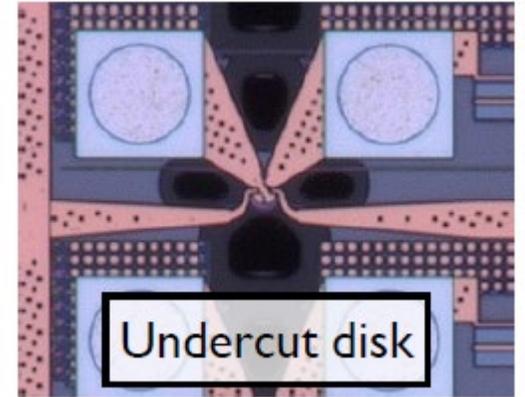


[Baehr-Jones JLT 2005]



- RRM resonance wavelength shifts with temperature due to the thermo-optic effect ( $dn/dT$ )
- Requires closed-loop control with local heaters
- Heater efficiency can be improved with undercut processing

Microdisk Modulator w/ Thermal Undercut



[Rizzo CLEO 2002]

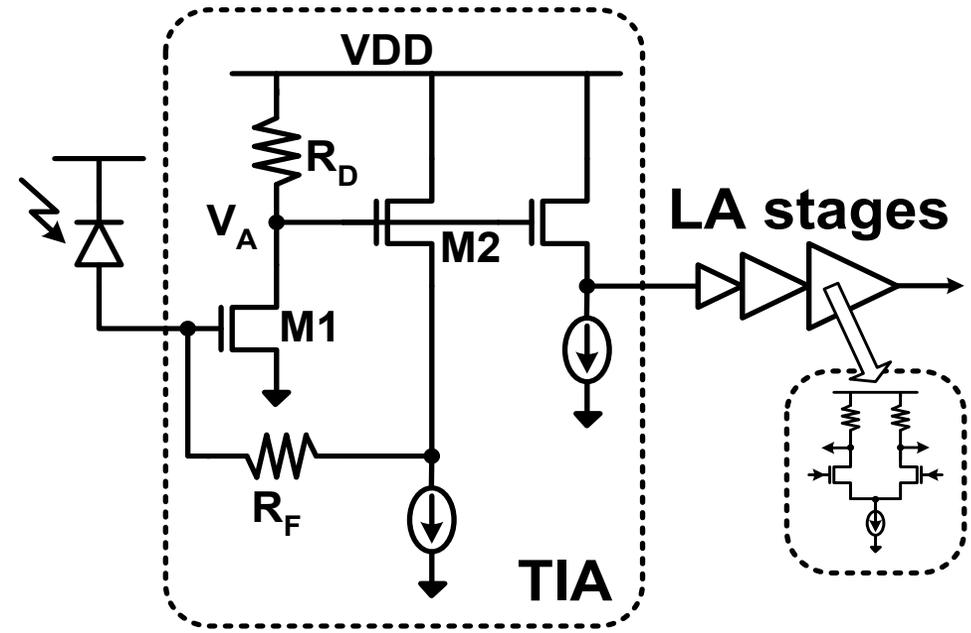
# Outline

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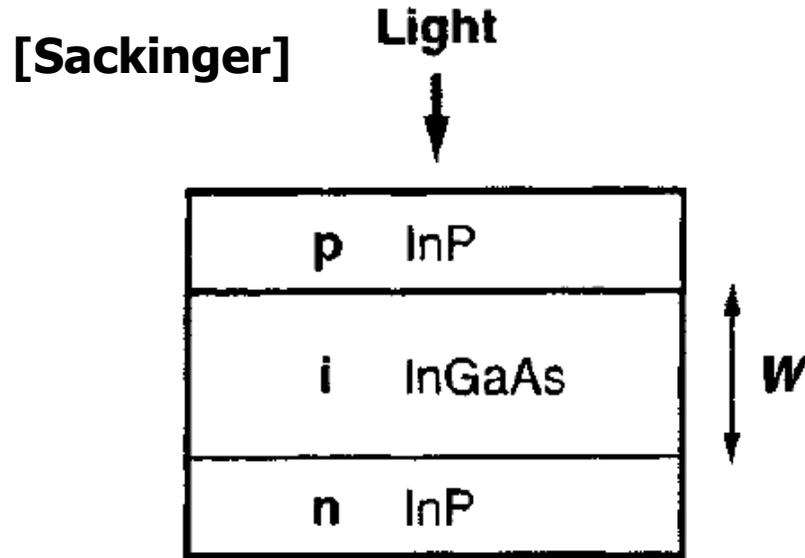
- Optical Interconnect Motivation
- Optical Channel Properties
- IMDD and Coherent Transceivers
- Transmitter Properties and Devices
- Receiver Architecture and Devices
- Conclusion

# Optical Receiver Technology

- Photodetectors convert optical power into current
  - Surface-normal p-i-n photodiodes
  - Integrated waveguide photodetectors
- Electrical amplifiers then convert the photocurrent into a voltage signal
  - Transimpedance amplifiers
  - Limiting amplifiers



# p-i-n Photodiode



## Responsivity:

$$\rho = \frac{I}{P_{opt}} = \frac{\eta_{pd} \lambda q}{hc} = 8 \times 10^5 (\eta_{pd} \lambda) \quad (\text{mA/mW})$$

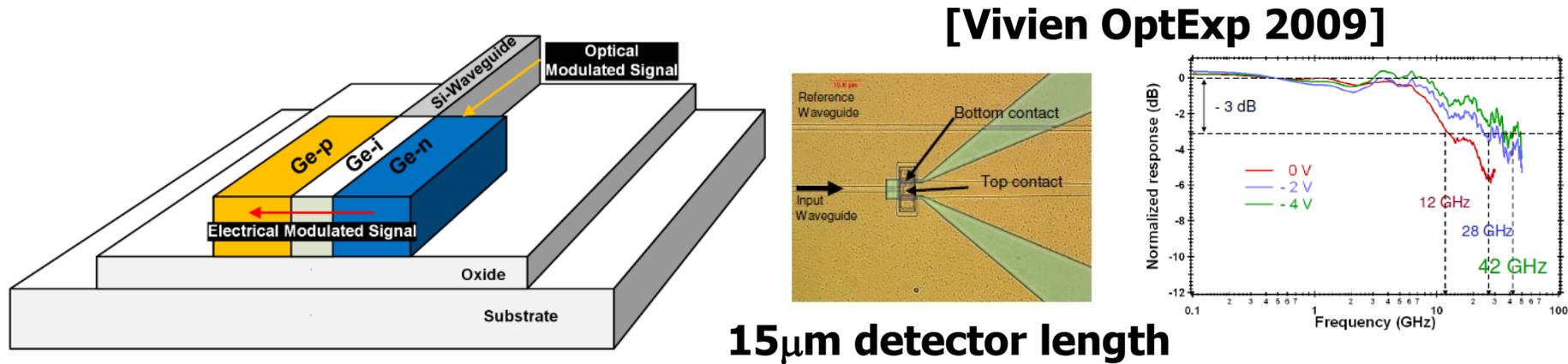
## Quantum Efficiency:

## Transit-Time Limited Bandwidth:

$$f_{3dBPD} = \frac{2.4}{2\pi\tau_{tr}} = \frac{0.45v_{sat}}{W}$$

- Normally incident light absorbed in intrinsic region and generates carriers
- Trade-off between capacitance and transit-time
- Typical capacitance  $\sim 100\text{fF}$  for 28Gb/s p-i-n PDs

# Waveguide p-i-n Photodetector



- A waveguide p-i-n photodetector structure allows this efficiency-speed trade-off to be broken
- The light travels horizontally down the intrinsic region and the electric field is formed orthogonal
- Allows for both a thin i-region for short transit times and a sufficiently long i-region for high quantum efficiency

# Conclusion

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- Optical fiber channels can support the required distances for large datacenters
- Directly-modulated laser-based transmitters are simple, but have chirp penalties and laser bandwidth limitations
- External-modulated transmitters generally have minimal chirp and higher bandwidth
- High-speed optical receivers need photodiodes with high responsivity and low capacitance